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(54) Title: MICROMECHANICAL TUNING FORK ANGULAR RATE SENSOR			
(57) Abstract A micromechanical tuning fork gyroscope includes a suspended structure (14) comprising at least first and second vibratable structures (38, 40). Each vibratable structure is energizable to vibrate laterally, within a first plane, along an axis (42) normal to the rotation sensitive axis (44). The lateral or inplane vibration of the first and second vibratable structures effects simultaneous vertical or rotational movement of at least a portion of the suspended structure upon the occurrence of angular rotation of the gyroscope about the rotation sensitive axis. Vertical or rotational movement of the suspended structure is sensed by electrodes (70, 72) and a voltage proportional to the movement is generated, for providing an indication of angular rate of rotation detected by the gyroscope.			

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MICROMECHANICAL TUNING FORK ANGULAR RATE SENSORFIELD OF THE INVENTION

This invention relates to angular rate sensors such as gyroscopes, and more particularly, to a micromachined tuning fork angular rate sensor fabricated from a unitary silicon substrate.

BACKGROUND OF THE INVENTION

Angular rate sensors such as gyroscopes serve as one of the major sensors in inertial navigation and guidance systems. Traditionally, gyroscopes have been implemented as large mechanical devices such as rotating wheel gyroscopes or other large metallic devices with dimensions of inches. These types of devices have several drawbacks including size restriction, reliability concerns due to the large number of mechanical parts, and high costs associated with precise machine tolerances and tuning.

The use of tuning forks for gyroscopes has been attempted but has been met with limited success. These devices are costly due in part to the effort required to tune the motor resonant frequency to the output resonant frequency and also in part due to the large size of such devices. Thus, large scale production of these types of devices have not proven commercially viable.

In addition, prior art tuning fork gyroscopes have not been able to separate or isolate the drive axis from the sense axis, leading to causing more difficult and complicated manufacturing techniques.

Although a number of attempts have been made to produce solid state, micromachined tuning fork gyroscopes, the prior art devices are made of quartz and still generally of intermediate size. In addition, precision fabrication and assembly techniques as well as assembly costs have limited the success of such devices.

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SUMMARY OF THE INVENTION

This invention features a monolithic, double tined, close-end, micromechanical tuning fork gyroscope, for detecting angular rotation about at least one rotation sensitive (sense) axis. Such a gyroscope is fabricated from a unitary silicon substrate in which has been selectively etched a pit over which is suspended a non-etched silicon structure.

The non-etched silicon structure is disposed within a first plane and includes at least first and second vibratable structures. The first and second vibratable structures are disposed generally adjacent and parallel to one another. Each of the first and second vibratable structures includes a mass integral with an associated vibratable structure.

In one embodiment, the non-etched silicon structure is suspended over the etched pit by first and second flexible elements which are disposed generally co-linear with the rotation sensitive axis of the gyroscope, for allowing the non-etched silicon structure to rotate about the rotation sensitive axis.

The non-etched silicon structure may be divided into at least two electrically isolated yet structurally coupled segments. Each segment includes one vibratable structure. The vibratable structures are energizable, in response to an applied voltage, to vibrate in a resonant or non-resonant mode parallel to a motor or drive axis oriented orthogonal to the sense axis.

Drive means energize the first and second vibratable structures to vibrate laterally, parallel to an axis normal to the rotation sensitive axis. Lateral vibration of the vibratable structures effects vertical or rotational movement of at least a portion of the non-etched silicon structure about the rotation sensitive axis upon the occurrence of angular rotation of the gyroscope about the rotation sensitive axis. Means for sensing rotation of the non-etched silicon structure are provided, for sensing vertical or

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rotational movement of the non-etched silicon structure, and for providing a voltage proportional to the rotational movement occurring in the non-etched silicon structure, for generating an indication of the angular rate of rotation detected by the tuning fork gyroscope.

DESCRIPTION OF THE DRAWINGS

These, and other features and advantages of the present invention will be better understood by reading the following detailed description taken together with the drawings, wherein:

Fig. 1 is a top view of a schematic representation of a double-tined, pivoting, closed-end tuning fork gyroscope according to one embodiment of the present invention;

Fig. 2 is a cross-sectional view of the gyroscope of Fig. 1 taken along lines 2-2;

Fig. 3 is an enlarged view of the electrical isolation gap and dielectric lap joint according to the present invention;

Figs. 4A-4C are top views of alternative designs for the isolation gap of the gyroscope according to the present invention;

Fig. 5 is a top view of a schematic representation of an open-ended tuning fork according to another embodiment of the present invention;

Fig. 6 is a top view of a schematic representation of a non-pivoting tuning fork gyroscope according to yet another embodiment of the present invention;

Fig. 7 is a cross-sectional view of a beam member of the gyroscope of Fig. 6 taken along lines 7-7;

Figs. 8A and 8B are schematic representations of several alternative methods of fabricating vibratable structures or tines for the gyroscope of the present invention;

Figs. 9A and 9B are schematic representations of a three axis instrument measurement unit including a plurality of

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micromechanical gyroscopes of the present invention along with other measurement devices;

Fig. 10 is a schematic representation of a pivoting, closed end, tuning fork gyroscope according to one embodiment of the present invention adapted for electromagnetic drive and electrostatic sense electronics;

Fig. 11 is a more detailed schematic representation of the electromagnetic drive and electrostatic sense electronics of Fig. 10;

Fig. 12 is a representation of a two-piece, pivoting, closed end, tuning fork according to another embodiment of the present invention incorporating electrostatic drive and sense electronics;

Fig. 13 is a more detailed schematic of the electrostatic drive and sense electronics of Fig. 12;

Fig. 14 is a schematic representation of a non-pivoting, closed end tuning fork according to yet another embodiment of the present invention including electromagnetic drive and electrostatic sense electronics;

Fig. 15 is a schematic of electromagnetic drive and electrostatic sense electronics including a closed-loop rebalancing circuit according to yet another embodiment of the present invention;

Fig. 16 is a top view of a schematic representation of an alternative, pivoting, tuning fork gyroscope according to the present invention adapted for electrostatic drive and sense electronics;

Fig. 17 is a schematic of the electrostatic drive and sense electronics for Fig. 16;

Fig. 18 is a more detailed schematic diagram of one embodiment of a vibratable structure for the tuning fork gyroscope of the present invention;

Fig. 19 is an illustration of an alternative embodiment of the gap between the vibratable structure and the tilt plate of a tuning fork gyroscope according to the present invention;

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Fig. 20 is a top view of a schematic representation of yet another embodiment of a pivoting, tuning fork gyroscope according to the present invention adapted for electromagnetic drive and electrostatic sense electronics;

Fig. 21 is a schematic of the electromagnetic drive and electrostatic sense electronics for the gyroscope of Fig. 20;

Fig. 22 is a cross-sectional view of a surface micromachined, micromechanical tuning fork angular rate sensor according to another embodiment of the present invention;

Fig. 23 is an expanded cross-sectional view of a layered or sandwiched construction of a micromechanical tuning fork angular rate sensor according to yet another embodiment of the present invention; and

Fig. 24 is a cross-sectional view useful in describing the micromechanical tuning fork angular rate sensor of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

There is shown in Fig. 1 a monolithic, double-tined, pivoting, closed-end tuning fork gyroscope according to one embodiment of the present invention. The tuning fork gyroscope is micromachined from a unitary silicon substrate employing the techniques of selective oxide removal, boron diffusions into the substrate through the removed oxide regions, and anisotropic etching. Such methods are known in the art and are further described herein and are also disclosed in Applicant's co-pending U.S. Patent Application No. 143,515 entitled "Method and Apparatus for Semi-Conductor Chip Transducer" which is incorporated herein by reference.

The etch stop diffusions and subsequent selective anisotropic etching create etch pit 12 having sloped sidewalls 16. Suspended over etched pit 12 is a non-etched silicon structure 14.

The non-etched silicon structure 14 includes at least first and second segments 18 and 20. First and second

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segments 18 and 20 are electrically isolated from one another by means of isolation gaps 22 and 24. The segments are structurally coupled by means of dielectric lap joints 26 and 28 (shown in dashed lines) which bridge the isolation gaps thereby structurally coupling the segments together while retaining electrical isolation.

The non-etched silicon structure 14 further includes first and second vibratable structures 38 and 40. The first and second vibratable structures 38 and 40 form the two "tines" or "forks" of the tuning fork gyroscope according to the present invention.

The first vibratable structure 38 is coupled to first segment 18 of the non-etched silicon structure, while the second vibratable structure 40 is coupled to the second segment 20 of the non-etched silicon structure. Thus, the two vibratable structures are electrically isolated from one another. The first and second vibratable structures 38 and 40 are energizable to vibrate in a resonant mode, and may be driven electrostatically or electromagnetically against each other parallel to an axis indicated by arrow 42 which is normal to the rotation sensitive or input axis of the gyroscope indicated by arrow 44. Excitation or drive signals, described in greater detail below, drive the two vibratable structures parallel to axis 42 by applying a sinusoidal voltage of opposite polarity to each of the structures.

For improved performance, however, it may be desirable to add additional mass at an appropriate location on the vibratable structures. This location is usually at the center of a closed-end tuning fork and at the end of an open-ended tuning fork. Typically, the mass should be symmetrical about the plane of motion to avoid unwanted torques on the gyroscope structure.

The oscillating or vibrating inertia of first and second vibratable structures 38 and 40 may thus be enhanced by adding masses 48 and 50 to the first and second vibratable

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structures respectively. Masses 48 and 50 are formed from silicon along with the non-etched silicon structure 14 by selective doping and subsequent anisotropic etching. Sensitivity of the gyroscope may be further enhanced by adding additional weight to masses 48 and 50 by plating gold, lead or a similar metal of high density. These metals and other high density metals may also be deposited by chemical vapor deposition proximate or within tub regions 52 and 54 formed in masses 48 and 50. By properly selecting the height of the plating and the area to be plated above the plane of the non-etched silicon structure, the center of gravity of the vibratable structures may be positioned within the plane of the flexures, thus balancing the masses about the plane of motion.

An important feature of the monolithic, micromechanical tuning fork gyroscope of the present invention is the ease of fabricating such a device from a single unitary silicon substrate. Utilizing conventional well known photolithography techniques applied to the surface plane of the wafer, great precision in locating the mass may be obtained.

In one nominal design, the non-etched silicon structure 14 measures approximately 800 microns in length by 500 microns in width, while masses 48 and 50 are approximately 80 microns wide by 50 microns long by 15 microns high, and weigh approximately 1.2×10^{-9} kg.

The first and second vibratable structures or forks are provided with enhanced flexibility in the direction parallel to axis 42 by choosing their geometry to include a high height-to-width ratio. In one design, each vibratable structure is approximately 4 microns wide by 15 microns high by 700 microns long. A gap of approximately 4 microns separates the two vibratable structures at their closest point.

The non-etched silicon structure 14 is suspended over etched pit 12 by means of flexible elements or pivots 56 and

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58. One end of each of the flexible elements 56 and 58 is attached to diametrically opposing sides of the non-etched silicon structure 14. The flexible elements are disposed generally co-linear with rotation sensitive or input axis 44. The second end of each of the flexible elements remains integral with silicon substrate 10. The flexible elements are typically doped with a P-type dopant for etch resistance, and are therefore electrically isolated from the N-type silicon substrate 10 by means of a PN junction which is formed between the P-doped flexible elements and the N type silicon substrate.

The boron diffusion used to define the non-etched silicon structure and the subsequent process of etching the surrounding silicon causes shrinking in the silicon lattice that creates a high tensile force in the flexible elements. Accordingly, tension relief beams 60 and 62 disposed proximate the first end of flexible elements 56 and 58 are formed by openings 64 and 66 in the non-etched silicon structure. Tension relief beams 60 and 62 serve to relieve the stress caused by the high tensile forces by allowing the tension relief beams to deflect or bow slightly, thereby reducing the torsional stiffness of flexible elements 56 and 58 and thus increasing the rotational sensitivity of non-etched silicon structure 14.

Tension relief beams and various embodiments thereof and a method for trimming the resonant frequency of a structure employing tension relief beams are described in greater detail in co-pending U.S. Patent Application No. 470,938 entitled "MICROMECHANICAL DEVICE WITH A TRIMMABLE RESONANT FREQUENCY STRUCTURE AND METHOD OF TRIMMING SAME" assigned to the assignee of the present invention, and which is incorporated herein by reference. Additionally, although first and second tension relief beams 60 and 62 are shown in this embodiment, only one tension relief beam is required to relieve the stress created by the high tensile forces in the flexures.

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During operation of the gyroscope of the present invention, any angular rotation of the gyroscope about rotation sensitive axis 44 imparts an out-of-plane motion perpendicular to the laterally vibrating structures 38 and 40. This motion produces a torsional motion in non-etched silicon structure or plate 14, effecting an oscillatory rotational movement of the non-etched silicon structure about the rotation sensitive axis 44 as shown by arrow 67. The outer regions 68 and 69 of the non-etched silicon structure 14 serve as "sense regions" of the gyroscope for detecting rotational motion resulting from an input angular rate. These "sense regions" may be thinner than the rest of the structure or alternatively, may include a "waffle" type construction, to minimize unwanted inertia effects.

In one embodiment, rotational sensing of the non-etched silicon structure 14 about the rotation sensitive axis 44 is accomplished utilizing bridge sense electrodes 70 and 72, although sensing and closed-loop rebalancing of the non-etched silicon structure 14 utilizing buried sense electrodes 74 and 76 is also contemplated by the present invention. Bridge electrodes 70 and 72 extend from silicon substrate 10, over etched pit 12 and continue extending over the non-etched silicon structure in the area of outer regions 68 and 69.

Typically, the bridge electrodes 70 and 72 are spaced approximately 2 to 10 microns above the non-etched silicon structure. The bridge electrodes are coupled to electrostatic sense electronics 78 which measure the amount of rotation of the non-etched silicon structure by sensing the differential capacitance between the sense electrodes and the adjacent non-etched silicon structure. Sense electronics 78, described in greater detail below, as well as drive and rebalance electronics may be formed on the silicon substrate adjacent to the tuning fork gyroscope of the present invention, or alternatively, may be located remotely from the gyroscope.

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The torsional rotation imparted onto the pivoting non-etched silicon structure 14 upon the occurrence of an angular rate input about rotation sensitive axis 44 is shown in greater detail in Fig. 2 wherein is shown flexible element 56 co-linear with rotation sensitive axis 44. Non-etched silicon structure 14 is torsionally displaced away from bridge sense electrode 70 and nearer to bridge sense electrode 72 upon the occurrence of angular rotation about rotation sensitive axis 44. Before forming the bridge electrodes, the planar surface of the silicon substrate 10 is thermally oxidized to form a dielectric layer 80 which electrically isolates the bridge electrodes from the substrate. One or more P+ doped buried electrodes such as electrodes 74 and 76 may be provided.

A portion of the double tined, closed-end micromechanical tuning fork gyroscope of the present invention is shown in greater detail in the cross-section of Fig. 3 wherein is more clearly illustrated electrical isolation gap 22 which serves to electrically isolate first non-etched silicon structure segment 18 and the attached first vibratable structure 38, from the second non-etched silicon structure segment 20 and the attached second vibratable structure 40. Electrical isolation gap 22 is formed by an intentional gap in the boron diffusion pattern utilized to form the non-etched silicon structure.

After the boron diffusion step but prior to anisotropic etch, dielectric lap joint 26 is formed over the electrical isolation slot by first depositing a layer of silicon nitride 80 of approximately 0.2 to 2.0 microns in thickness. Subsequently, a layer of silicon dioxide 82 of from 0.5 to 5 microns in thickness may be applied over the silicon nitride layer to stiffen the dielectric lap joint. By minimizing the width of the electrical isolation gap 22 to approximately 5 microns or less in the underlying silicon structure, and by applying dielectric lap joint 26, a rigid and structurally coupled but electrically isolated non-etched

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silicon structure results. The subsequent process of anisotropic etching undercuts the silicon structure forming the electrical isolation gap 22.

5 As shown in Fig. 1, isolation gap 22 is a diagonal gap in the non etched silicon structure 14. The tuning fork gyroscope of the present invention also contemplates other embodiments of the gap including a straight gap 22a shown in Fig. 4A, and the undulating and non-straight isolation gaps 22b and 22c shown in Figs. 4B and 4C, which provide greater
10 resistance to bending than does gap 22a.

An additional embodiment of a tuning fork gyroscope according to the present invention is shown in Fig. 5 wherein is illustrated an open-ended tuning fork fabricated from a unitary silicon substrate. The gyroscope 100 includes a non-
15 etched silicon structure 102 suspended over an etched pit 104 anisotropically etched from the silicon wafer.

Non-etched silicon structure 102 includes first and second vibratable structures or forks 106 and 108 coupled to a rigid connecting segment 110. A second pair of vibratable
20 structures or forks 112 and 114 are also coupled to rigid connecting segment 110.

The first and second vibratable structures 106,108 and rigid central connecting segment 110 are formed by relatively deep Boron diffusions yielding structures with a height-to-
25 width ratio of greater than 1. This high height-to-width ratio gives the first and second vibratable structures 106,108 a preferred oscillation in a direction of arrow 116. In addition, performance of the gyroscope according to this embodiment may be enhanced by providing masses 118 and 120
30 at the ends or tips of the vibratable structures 106,108 respectively.

Applying a drive input voltage to protruding cantilevered electrodes 122 and 124 will cause the first and second vibratable structures 106,108 to vibrate in a
35 direction of arrow 116. Electrodes 122 and 124 are formed by the same diffusion that is used to form structure 110.

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In response to angular rotation about input axis 126, an oscillatory torque will be applied to the rigid central segment 110. This oscillatory torque will cause the second pair of vibratable structures 112,114, having a low height-to-width ratio, to resonate in a vertical direction, perpendicular to the plane of the device and perpendicular to the lateral oscillation in a direction of arrow 116 of the first and second vibratable structures 106,108.

The amplitude of the oscillation in the second set of vibratable structures 112,114 is proportional to the angular rate, and is sensed by sense electronics 128 by applying a high frequency out-of-phase signal from sense input 134 to vibratable structures 112,114 through buried electrodes 130,132.

The structure may also include at least one opening 136 which forms tension relief beam 138 for relieving stress form due to the Boron diffusions. Further, since the semiconductor material is N type and the non-etched silicon structure 102 and bridge electrodes 122,124 are P type, all structures are electrically isolated from the body of the silicon wafer by the PN junction formed between the P type structure and the N type silicon wafer.

An additional embodiment of a positioning monolithic, micromechanical tuning fork gyroscope according to the present invention is shown in Fig. 6 and includes, among other elements, first and second vibratable structures 150 and 152. Each vibratable structure includes a mass such as mass 154 coupled to first and second beams 156 and 158. The mass and attached beams vibrate as an entity with the beams operating as springs, which avoids the problem of the mass not being perfectly centered about the vibrating beam and thereby causing unwanted torques. In the case of a non-pivoting structure, the mass is disposed about the center of the tine. For readout purposes, bridge electrodes (not shown) may be provided to sense the motion of the mass by

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measuring capacitance between the electrodes and sense regions 160,162.

5 Lateral and vertical vibration of the vibratable structures 150 and 152 are facilitated by the geometry of the beams, such as beam 164 which is shown in cross-section in Fig. 7. Beam 164 includes first and second segments 166,168 which have a high height-to-width aspect ratio which is typically greater than 1. The high aspect ratio of these sections of the beam provide added flexibility in the lateral direction, within the plane of the device as indicated generally by arrow 174, while also providing increased resistance to vertical motion, perpendicular to the plane. In contrast, segments 170 and 172 have a much lower height-to-width ratio, on the order of 0.5 or less, which facilitates movement in the vertical direction indicated generally by arrow 176. The lower height-to-width ratio segments of the beam therefore resists movement in the lateral direction, parallel to the plane.

10 The use of deep boron diffusion to form the flexible tines or vibratable structures 38 and 40 of the tuning fork requires a significant gap, on the order of three microns, between the tines to insure that they do not diffuse together. Additionally, the boron also diffuses outwardly away from the original photolithographic line. This tends to limit or reduce the desired height-to-width ratio which allows the tines to be flexible in the lateral direction but stiff in the vertical direction.

20 The tuning fork gyroscope according to the present invention requires that the vibratable structures have a preferred mode of resonance parallel to the plane of the device. Accordingly, the height of the tines or beams which comprise a portion of the vibratable structures is preferred to be greater than their width, thus, a structure with a high aspect ratio. Vibratable structures comprised of high aspect ratio beams may be fabricated by selective boron diffusions through a slot in the silicon and the silicon oxide,

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selective epitaxial back filling and capping with another boron diffusion and subsequent anisotropic etching to define a beam with an aspect ratio of up to 10-to-1. Such a method is described in Applicant's co-pending U.S. Patent Application Serial No. 07/599,131 entitled "MONOLITHIC MICROMECHANICAL VIBRATING STRING ACCELEROMETER WITH TRIMMABLE RESONANT FREQUENCY" which is incorporated herein by reference.

Several additional methods may be utilized to fabricate tines or beams of varying aspect ratios. For example, two relatively shallow P+ Boron diffusions 180 and 182, Fig. 8A, may be provided in the N substrate 183. Anisotropic etching using a standard EDP process will result in two tines or beams defined generally by the P+ Boron doped areas 180, 182, with an aspect ratio on the order of 0.5. Although not a very high aspect ratio, such beams might be useful as the main vibratable structures of a tuning fork according to the present invention, or as a lower aspect ratio portion of a beam such as beam 164, Fig. 7.

An additional method of fabricating tines is illustrated in Fig. 8B and includes applying a very deep Boron diffusion in the area defined by line 184. Subsequently, a plasma etching process is used to cut through the etch resistant Boron doped material in areas 186. A subsequent EDP etch can then be used to undercut the structure leaving tines 188, 190 with a high aspect ratio. Aspect ratios of 1 to 4 are generally possible with this process.

One feature of the micromechanical, monolithic tuning fork gyroscope of the present invention is the ability to provide drive and sense electronics on the semiconductor substrate itself that includes the gyroscope. Thus, one integral package includes both the gyroscope and the necessary drive and sense electronics. In addition, two gyroscopes, one disposed orthogonal to the other, may be located on one substrate, thus allowing for two input axes on one substrate. Further, by providing a second tuning fork

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gyroscope substrate according to the present invention disposed in a plane perpendicular to the first substrate, a three axis tuning fork gyroscope system with one redundant axis may be constructed.

5 For example, a first silicon substrate 300, Fig. 9A, mounted to mounting block 302 or other device includes first and second gyroscopes with mutually orthogonal in plane input axes as shown by arrows 304 and 306. By providing a second semiconductor substrate 308 mounted in a plane perpendicular
10 to the mounting plane of first substrate 300, a third gyroscope with an in plane input axis parallel to arrow 310 provides a complete three axis gyroscope system with one input axis 312, parallel to axis 304, which is redundant or unused. Thus, only two mounting surfaces are required to
15 provide a three axis gyroscope system.

 In a further embodiment, silicon substrate 320, Fig. 9B may include a first gyroscope 322 which has an out-of-plane input axis perpendicular to the planar surface of substrate 320 parallel to arrow 324. Such a gyroscope is described in
20 U.S. Patent No. 4,598,585. In addition, gyroscopes 326 and 328 according to the present invention each with an in-plane input axis, provide a 3-axis gyroscope system on one, semiconductor substrate.

 The substrate also includes first and second in-plane sensing accelerometers 330,332 such as a vibrating string accelerometer disclosed in co-pending U.S. Patent Application
25 Serial No. 07/599,131, entitled: MONOLITHIC MICROMECHANICAL VIBRATING STRING ACCELEROMETER WITH TRIMMABLE RESONANT FREQUENCY which is incorporated herein by reference. Also
30 included is a third accelerometer 334 having an out-of-plane input axis. Such an accelerometer is disclosed in co-pending U.S. Patent Application Serial No. 07/528,051, entitled: ADVANCED MICROMECHANICAL ACCELEROMETER which is also
35 incorporated herein by reference. Thus, by further providing the three orthogonally sensing accelerometers 330,334 a complete, three axis instrument measurement unit including

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all drive and sense electronics is provided on one substrate 300.

5 Various drive and sense electronics as well as a number of modes of operation may be utilized with various embodiments of the tuning fork gyroscope according to the present invention. For example, the tuning forks may be driven and sensed electromagnetically or electrostatically; in either open or closed loop; and the gyroscope may be designed to be self-oscillatory wherein an electronic loop
10 may be used to maintain the tuning fork gyroscope at its natural or resonant frequency over a wide temperature range. In addition, consideration must be given to whether the tuning fork gyroscope will be fabricated on a pivoting plate supported by flexures or whether a non-pivoting device will
15 be utilized.

The choice between pivoting and non-pivoting tuning fork gyroscope configurations depends on a number of factors. For example, an advantage of the pivoting structure is that the lateral vibration of the tuning forks is separated from
20 vertical movement on the plate which results from rotation of the gyroscope about the input axis. Since the gyroscopic forces on the tuning forks are transmitted to the pivoting structure or plate, it is therefore not necessary to detect the bending or vertical deflection of the tines themselves. Accordingly, the tines do not have to do double duty,
25 vibrating laterally and deflecting vertically in a manner that lends itself to readout. Instead, vertical movement is turned into an angular deflection of the plate or non-etched silicon structure which is therefore only dependent upon the flexures which connect the plate to the silicon frame. The
30 flexures can therefore be properly and advantageously designed independently of the tuning forks.

35 Additionally, in a pivoting gyroscope, the plate area can be made arbitrarily larger than the tuning forks, since it does not play a part in the gyroscopic action. This means

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that there will be a much larger readout sensitivity for the pivoting gyroscope than for the non-pivoting version.

Several of the many possible combinations of gyroscope electronics and construction configurations will be detailed below for illustrative purposes, although many more combinations are possible and contemplated by the present invention. In the first example, pivoting gyroscope 200, Fig. 10, is illustrated with electromagnetic drive electronics 202 and electrostatic sense electronics 204. Drive electronics 202 apply an AC voltage to flexure 206 which is coupled to rotatable plate 208. Plate 208 includes a high conductive layer or wire 210 which begins at one end of flexure 206, but not on the flexure itself. Wire or conductive layer 210 splits symmetrically and passes on or through the first and second vibratable structures or forks 212, 214, then recombines into a single wire terminating at the second flexure 216. Output 218 from the second flexure 216 is then coupled to electrostatic sense electronics 204 which provides an output voltage signal 220 whose voltage is proportional to the input rate. This signal is subsequently processed utilizing well known signal processing techniques to provide the gyroscope output signal.

Tuning fork gyroscope 200 is also provided with electrodes 222a, 222b, 224a, 224b, and 226a, 226b. Electrodes may be disposed either below plate 208 (buried electrodes) or above plate 208 (bridge electrodes), and are arranged symmetrically along both sides of the plate. The electrodes are used for torquing the plate in the case of a closed-loop mode, and for sensing the angular displacement of the plate. Dielectric isolation gaps 228 and 230 are provided to eliminate any potential voltage gradient on plate 208.

A more detailed schematic representation of electromagnetic drive and electrostatic sense electronics 202 and 204 is shown in Fig. 11 wherein an AC drive voltage E_r from voltage source 232 is applied through resistor 234 to the tuning forks 212, 214 and plate 208, all represented by

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signal path 236. Drive voltage E_f , typically 1-10 volts at 1-10 KHz causes tuning forks 212, 214 to vibrate laterally. An excitation voltage source 238 provides an excitation voltage E_x , typically 1 volt at .1 to 1 Mhz, which serves as a reference signal to indicate rotational movement of plate 208 caused by an input rate about the sense axis. The inverted and non-inverted signals are applied to opposite sides of the tuning fork structure. If it is desired to operate the device in a closed-loop mode, two torque and bias voltages E_{t1} , V_1 and E_{t2} , V_2 , 240-246 respectively, are provided to rebalance the rotational movement of the plate in phase and in quadrature with the vibration of the forks as will be explained in greater detail below.

The operation of the circuit is dependent upon the fact that output 218 from the flexures 216 is driven to virtual ground by the feedback circuit of operational amplifier 248. Angular rate causes the deflection of the tiltplate 208. The tilt is caused by the torque exerted upon the tiltplate from gyroscopic forces when there is an angular rate about the input axis. The tilt of the plate is measured by the capacitor sensor system made up of electrodes 222a, 222b, 224a, 224b, 226a and 226b as shown. The electrodes may also be used to torque the plate externally such as when a rebalance loop is used as described below.

The angle of rotation of the tiltplate is sensed by exciting one set of electrodes with E_x , a high frequency AC signal. By demodulating the signal using demodulator 250, with respect to the vibration frequency ω_x of the tuning forks, an envelope or modulating signal e_{o2} is recovered and provides a voltage proportional to the tilt angle. This voltage is proportional to the input rate when the gyroscope is operated in the open loop mode or, when the gyroscope is operated in the closed loop mode, the voltage is used to provide a signal to rebalance the tiltplate by means of the above mentioned electrodes.

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The torquing voltage is proportional to the applied torque on the tiltplate by virtue of a conditioning system which makes use of the relations in the following equations to convert the square law force-voltage relationship for a capacitor into a linear voltage-torque relationship.

$$e_{22a} = -E_x; e_{22b} = E_x \quad (1)$$

$$e_{224a} = -E_{T1} - V_1; e_{224b} = E_{T1} - V_1 \quad (2)$$

$$e_{226a} = -E_{T2} - V_2; e_{226b} = E_{T2} - V_2 \quad (3)$$

$$ST = (e_{22a}^2 - e_{22b}^2) + (e_{224a}^2 - e_{224b}^2) + (e_{226a}^2 - e_{226b}^2) \quad (4)$$

$$ST = E_x^2 - E_x^2 + (E_{T1} - V_1)^2 - (E_{T1} - V_1)^2 + (E_{T2} - V_2)^2 - (E_{T2} - V_2)^2 \quad (5)$$

$$ST = +4E_{T1}V_1 + 4E_{T2}V_2 \quad (6)$$

A tuning fork gyroscope according to the present invention utilizing electrostatic electronics for both drive and sensing is illustrated in Fig. 12 by a pivoting closed-end tuning fork gyroscope 252. The gyroscope includes plate 254 comprised of two halves, each half electrically isolated by means of gaps and lap joints 256, 258. In this embodiment, inverted and non-inverted driving voltages are applied to the flexures. The inverted and non-inverted driving voltages cause the tuning fork structure, which looks capacitive as represented by capacitor C_f , Fig. 13, to vibrate laterally. As in the previous embodiment describing electromagnetic electronics, an excitation voltage E_x as well as a bias voltage B , typically 5 volts, are provided. The voltages (V) across capacitors $C3a$ - $C5b$ are represented by equations 7-12 below.

$$V_{C3a} = (-E_f - E_x - B) - (-V_1) \quad (7)$$

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$$V_{CSa} = (-E_f - E_x - B) - (-V_2) \quad (8)$$

$$V_{CSb} = (E_f + E_x + B) - (-V_1) \quad (9)$$

$$V_{CSb} = (E_f + E_x + B) - (-V_2) \quad (10)$$

$$V_{C4a} = -(E_x + E_f + B) \quad (11)$$

$$5 \quad V_{C4b} = (E_x + E_f + B) \quad (12)$$

The torque (ST) measured by the gyroscope is illustrated by equations 13-15.

$$\begin{aligned} ST_1 &= [-(E_f + E_x + B) + V_1]^2 - [(E_f + E_x + B) \\ &\quad + V_1]^2 = -4V_1 [E_f + E_x + B] \end{aligned} \quad (13)$$

$$\begin{aligned} 10 \quad ST_2 &= [-(E_f + E_x + B) + V_2]^2 - [(E_f + E_x + B) \\ &\quad + V_1]^2 = -4V_2 [E_f + E_x + B] \end{aligned} \quad (14)$$

$$\begin{aligned} ST &= ST_1 + ST_2 = -4[V_1B + V_2B + E_f(V_1 + V_2) \\ &\quad + E_x(V_1 + V_2)] \end{aligned} \quad (15)$$

15 An additional embodiment of the tuning fork gyroscope of the present invention is illustrated as a closed end, non-pivoting micromechanical tuning fork gyroscope 260, Fig. 14. In contrast to a pivoting plate gyroscope previously described in conjunction with Figs. 10 and 12 wherein angular rotation about the input axis produces a tilt or rotation in the plate, the tuning forks in non-pivoting gyroscopes experience an upward force on one fork while the other fork experiences a downward force. Thus, the non-pivoting tuning fork gyroscope 260 includes two parallel vibratable structures or forks 262 and 264 which are driven by an AC voltage source (E_f) 266. The voltage causes the tuning forks to vibrate laterally, in the plane of the structure. Angular

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rotation about the gyroscope's input axis indicated generally by arrow 268 causes the tuning forks to vibrate in a vertical direction, perpendicular to the lateral direction.

Angular rotation or readout is performed electrostatically by one or more electrodes above or below the tines such as electrodes 270 and 272 and utilizing the illustrated circuit which is similar to the circuits previously described.

As previously discussed, the tuning fork gyroscope and electronic circuits of the present invention can be operated in two modes namely, closed-loop or open-loop. The circuit described in connection with Figs. 10 and 11 illustrates an open-loop mode configuration. A closed-loop circuit is illustrated by box 274, Fig. 15 wherein there are four inputs namely E_{T1} ($W_v 0$ or vibration frequency angle 0), E_{T2} ($W_v 90$ or vibration frequency, angle 90), V_1 and V_2 . Output 276 from the gyroscope is an AC signal, carrier modulated. This signal is then demodulated and filtered by demodulator/filter 278, against the excitation signal E_x which strips out the carrier. This produces an AC signal 280 at the vibration frequency which has an amplitude proportional to the angular rate of the gyroscope. The signal is then AC amplified by amplifier 282 and again demodulated and filtered against the vibration frequency at angle 0 by demodulator/filter 284, and against the vibration frequency at angle 90 by demodulator/filter 286. The output signals from demodulator/filters 284, 286 are then conditioned which provide quadrature and gyroscope signals 288 and 290 respectively which are fed back to the input of the gyroscope so that the plate is maintained at AC null in both phases. The gyroscope signal output 290 is the desired gyroscope output, whose voltage is proportional to the angular input rate.

The circuit described in conjunction with Fig. 15 applies when the vibration frequency of the tuning forks or vibratable structures is not equal to the natural frequency

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of the pivoting gyroscope plate. The electronics may also be suitably modified to allow operation when the vibration frequency of the tuning forks is equal to the natural frequency of the gyroscope plate. Such a modification is well known to those skilled in the art.

An additional embodiment of the micromechanical tuning fork gyroscope of the present invention is shown in Fig. 16. The selection of such an embodiment is driven by the desire to maximize the sensitivity of the device. To achieve this goal, the desire is to maximize the gyroscopic torque on the pivoting tilt plate 354.

As shown in equation 16 below, if all the inertia of the tuning fork gyroscope according to the present invention were concentrated in the tuning forks or vibrating tines themselves, then the gyroscopic torque produced when an input rate is applied is shown in equation 16 where I_1 is the change in the moment of inertia about the input axis (I_x) as the tuning fork oscillates.

$$\text{Gyroscopic torque} = \frac{I_1}{I_x} \omega_t \omega_x \cos \omega_t t \quad (16)$$

where

$$I_1 = DI_x = 2Mr Dr;$$

ω_t is the tine frequency;

t is time;

ω_x is the input rate;

M is the mass of the tuning forks; and

r is the deflection of the tine along the Y axis.

Since r is the deflection of the tuning fork tine, the tines should be located as far apart as possible to maximize the gyroscopic torque for a given deflection of the tines. Stated differently, the force on the tines from the

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gyroscopic action is fixed for a given tine deflection and therefore, by placing the tines as far as possible from the axis of rotation, the torque on the tilt plate is maximized. The larger gyroscopic torque in effect increases the angular momentum which results in more volts per unit rate input, raising the signal level, reducing the gyroscope's sensitivity to Brownian noise, thus making design of the gyroscope and the electronics easier.

As shown in Fig. 16, the vibrating tines 350,352 represented, for the sake of simplicity, by simple bars F and G, are located on the extreme edge of tilt or pivoting plate 354. The tines are electrically isolated from the rest of the tilt plate by dielectric or P-N isolation regions 356a-356d. The tines are connected by a wire 358 which is dielectrically isolated from the rest of the structure and connected to input flexure pivot 360 (E) also dielectrically isolated from the remainder of the structure. Wire 358 places a common input voltage E_i on each vibrating tine 350,352.

Output flexure pivot 362, also dielectrically isolated, in turn is connected to the input node (N) of operational amplifier 364 as will be further explained below. Thus, the potential of tilt plate 354 is driven to that of the operational amplifier input node (N) which in turn is driven to virtual ground by the feedback configuration of operational amplifier 364.

Upon application of a sinusoidal voltage (E_i) on input flexure 360 (E) an electrostatic force is generated between the tines 350,352 and the adjacent tilt plate 354 due to the potential difference between the tines and the tilt plate. This voltage potential difference will cause the tines to vibrate at an amplitude which is dependent upon the applied voltage, the frequency of the applied voltage, and the mechanical characteristics of the tines.

To minimize the required tine drive voltage, it is most desirable to drive the tines at their resonant frequency.

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In order to accomplish this, the displacement distance moved by the tines must be measured. This may be accomplished by the circuit shown in accompanying Fig. 17 including the loop formed by E, N, I and E_x .

5 In this circuit, an AC voltage E_x at a typical frequency of greater than 100 KHz, which is much higher than the resonant frequency of the tines, typically 3 to 10 KHz is applied as shown. This AC signal is used as a carrier and is modulated by the tine vibration.

10 The capacitance labeled C_t is the capacitance of the tine gap. A change in capacitance C_t is a function of the displacement of the tines. Thus, the output voltage of operational amplifier 364 is proportional to the capacitance C_t of the tines, and the change in the output voltage of the
15 operational amplifier is similarly proportional to the change in capacitance C_t of the tines. Since the output of the operational amplifier is a function of the tine capacitance, the output can be used to provide an indication of tine position. This may be done by demodulating the output 366
20 of the operational amplifier with respect to the tine excitation frequency w_x . The output (I) 368 of the demodulator is appropriately modified by feedback network 370 to provide the tine voltage E_t . This will cause the tines to oscillate at their resonant frequency w_t . A fixed bias
25 voltage B_t of typically 1-10 volts, is also summed in with the tine voltage E_t and the tine vibratory frequency E_x to linearize the force characteristics.

As a result of an input rate along the gyroscope's input axis, the tilt plate 358 will oscillate about the input axis
30 indicated generally by arrow 372, with the angle of vibration proportional to the input rate. This angle or amount of vibration of the tilt plate must then be measured. This may be accomplished by including sense electrodes 374, 376 which may run over (bridge) or under (buried) tilt plate 358. The
35 sense electrodes are represented as nodes A and B in the circuit diagram of Fig. 17.

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An AC excitation voltage E_x of frequency w_x , typically equal to or greater than 100 KHz, and much higher than the vibration frequency but different than the tine excitation frequency w_x is applied. The AC excitation voltage E_x is applied directly to one sense electrode and inverted with respect to the other electrode.

When the tilt plate is level, that is, no input angular rate is present, the capacitances between the two sense electrodes and the tilt plate are equal and therefore, there is no output from operational amplifier 364. When the plate tilts as a result of an input angular rate, the capacitances C_{s1} and C_{s2} change differentially and therefore, a voltage is generated by operational amplifier 364 which is proportional to the difference in capacitances. The output of operational amplifier 364 is demodulated by demodulator 378 with respect to the tine excitation frequency w_x to provide an output signal 380 that is a function of the tilt angle of the plate and thus, a function of the input angular rate.

Further, torquing electrodes 382, 384, labeled as nodes C and D, are provided to enable a rebalance torque to be applied to the tilt plate. As shown in Fig. 17, a rebalance voltage E_R and a linearizing bias B_R are summed and applied to the torquing electrodes.

In the embodiment described immediately above, discussions were focused on the gyroscope in general, the tines having been represented as simple bars. In a preferred embodiment, however, such a structure would not afford as efficient of a vibratable structure as desired. The most efficient vibratable structure must be flexible horizontally that is, within the plane of the device, while rotationally and vertically stiff.

Accordingly, the preferred embodiment of a pivoting, micromechanical tuning fork of the present invention includes the tine structure shown generally in Fig. 18 which includes a mass 400 attached to tilt plate 402 by means of four tines 404a-404d which act like "springs". A capacitive gap

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indicated generally by arrow 406 is formed between the mass and the adjacent plate 402. Tines 404a-404d are high aspect ratio beams and provide no other function other than to allow the mass to vibrate parallel to axis 408. The vibrating frequency of such a vibratable structure is a function of this supporting tines 404a-404d and the central mass. The mass of the supporting tines is negligible. This avoids undesirable effects that might occur due to multi-mode vibration of the supporting tines or springs. Further, the vertical rigidity of the supporting tines in all directions but laterally means that there will be no problems with other resonants either vertically, out of plane or rotationally. This approach is in accordance with the desired principal of isolation, which requires one function for each structural element. Further, the four supporting tine structures provide the most rotational stiffness which tends to minimize effects due to mass unbalance.

Although capacitive gap 406 is formed by simple parallel structures, an alternative embodiment includes the interdigital gap structure shown in Fig. 19.

An additional embodiment of a pivoting, micromechanical tuning fork according to the present invention is illustrated in Fig. 20 which, although similar to the pivoting tuning fork gyroscope shown in Fig. 16, is adapted to utilize electromagnetic drive and electrostatic sense and rebalance torquing electronics. In this embodiment, the vibrating tines such as tine 410, again illustrated as a simple bar for the sake of simplicity, is disposed between two conductive electrodes 412, 414. The tines are driven electromagnetically by properly controlling the direction of current flow through the tine and the adjacent conductive regions of the tilt plate.

The direction of current flow is best illustrated by the schematic diagram of Fig. 21. To fabricate such a structure, the tines may be sufficiently doped to carry enough current. Alternatively, an electrically isolated metallization layer

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may be deposited on top of the tines. Similarly, the areas of the tilt plate adjacent the vibrating tines may be similarly doped or include electrically isolated metallization layers. Electrostatic sense and torquing electronics, similar to those described in conjunction with Fig. 17 are contemplated.

Although specific features of the invention are shown in some drawings and not in others, this is for convenience only as each feature may be combined with any or all of the other features in accordance with the invention. Additionally, although the structure of the present micromechanical tuning fork angular rate sensor has been described in conjunction with a structure a unitary silicon substrate and anisotropic etching, this is not a limitation of the present invention.

For example, in addition to the silicon bulk micromachining and anisotropic etching techniques described above, the structure and fabrication of a vibrating structure on a gimbal as an angular rate sensor of the present invention may be fabricated from various other techniques. These include defining the vibrating and gimbal components by reactive ion etching of the surrounding silicon after diffusing with Boron as a P+ region to form the broad outline of the structure, followed by anisotropic etching. The device may be built up from the surface of a material as in the case of selectively applying polysilicon over a silicon wafer. Further, bonding techniques may be utilized to create a layered or sandwiched structure utilizing silicon, glass and quartz.

For example, an alternate method of fabricating a micromechanical tuning fork angular rate sensor according to the present invention includes a surface micromachining process which builds up the structure forming the tuning fork angular rate sensor as opposed to building the structure from the top down as described above in conjunction with selective anisotropic etching techniques.

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As shown in Fig. 22, this embodiment of the tuning fork angular rate sensor 500 is fabricated by first providing a substrate 502 which may be silicon. A thin layer 504 of silicon nitride is applied over the substrate 502 to protect the substrate from subsequent processing.

Next, a sacrificial layer 510 is applied over the substrate. It is patterned to remain temporarily where gaps or undercutting are required between the tines and the substrate. The sacrificial layer may include a CVD glass layer of approximately two microns in thickness. The CVD glass sacrificial layer etches very rapidly in a buffered HF water etch solution.

A thick layer of polysilicon 512 is then deposited over the sacrificial layer 510 and its upper surface 514 oxidized. The surface oxide is patterned and used as a mask to plasma etch the polysilicon layer 512 leaving only the tines 516a, 516b of the tuning fork angular rate sensor and flexures (not shown) which couple the tines to the substrate. In the case of open ended tines, one flexure is provided proximate one end of the tines. In the case of close ended tines, two flexures are provided, one proximate each of the two ends of the flexures. The sacrificial layer 510 is then etched away to undercut and release the tines. Using this method, aspect ratios of 1 to 4 for the tines as well as other structures may be achieved.

Additionally, read-out electrodes may be provided which are implemented as P/N junctions under the device, as a thin layer of metallization or a thin layer of polysilicon under the sacrificial layer 510.

Yet another embodiment of the present invention contemplates the fabrication of a tuning fork angular rate sensor utilizing a layered or sandwiched method. As shown in Fig. 23, the tuning fork angular rate sensor 520 includes a base electrode layer 522 over which is applied a beam layer 524 followed by a top electrode layer 526. According to this technique, this embodiment of the micromechanical tuning fork

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angular rate sensor allows beam layer 524 to be fabricated utilizing any one of the many etching techniques now known or which may be discovered in the future to completely etch through a thin wafer. Oxide or plated spacers 528a-528d are provided proximate beam layer 524 to allow the tuning forks to vibrate and rotate as previously described. Electrodes 530 and 532 are contained on the top and base electrode layers 526, 522 respectively. The electrodes may include doped silicon regions in the case of silicon layers or deposited metallized electrodes in the case of glass or quartz layers. Well known wafer bonding techniques are utilized to bond the wafers or layers together.

These, and other structures and fabrication techniques for the realization of a gimballed vibrating pair of structures are discernable by reference to Fig. 24. As shown there, first and second vibrating bands 540, 542 with or without additional masses, are fixed to or within a gimbal ring 544, which is in turn attached to a surrounding plate or platform via flexures 546 located within a central zone 548.

In the first embodiment, the elements 540, 542, 544 and 546 are defined by Boron diffusions and the elements are released from the surrounding semiconductor by anisotropic etching.

In a further embodiment, a substantial portion of the surface including the elements 540, 542, 544 and 546 are Boron doped. A reactive ion etch (RIE) then erodes deep pits to define the elements 540, 542, 544 and 546 with high aspect ratios (height to width), etching then frees the undersurfaces.

In yet another embodiment, a layer including the elements 540, 542, 544 and 546 is grown as polysilicon over a layer 550 of oxide on an underlying silicon substrate 552. The elements 540, 542, 544 and 546 are then defined by RIE etching the surrounding silicon and chemically removing the oxide layer.

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In a further embodiment, the elements 540, 542, 544 and 546 are exposed in an RIE etch and then doped with Boron. A subsequent etch frees the desired structure.

5 In a fifth embodiment, the elements 540, 542, 544, 546 are vapor deposited around and on patterns formed in photo resistant and/or oxide which are then chemically removed to leave the gimbaled structure.

Electrodes can be formed using the isolation techniques and bridge or buried electrode designs shown above.

10 Modifications and substitutions by one of ordinary skill in the art are considered to be within the scope of the present invention which is not to be limited except by the claims which follow.

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CLAIMS

1. A monolithic, micromechanical tuning fork gyroscope, for detecting angular rotation about at least a first rotation sensitive axis, comprising:

5 a silicon substrate in which has been selectively etched a pit, and over which is suspended a non-etched silicon structure;

10 said non-etched silicon structure disposed within a first plane and including at least first and second vibratable structures, said first and second vibratable structures disposed generally adjacent and parallel to one another;

15 drive means, for energizing said first and second vibratable structures to vibrate laterally along an axis normal to said rotation sensitive axis and within said first plane, said lateral vibration of said first and second vibratable structures effecting simultaneous vertical movement parallel to a second plane and normal to said first plane of at least a portion of said non-etched silicon structure upon the occurrence of angular rotation of said gyroscope about said first rotation sensitive axis; and

20 means for sensing said simultaneous vertical movement of said at least a portion of said non-etched silicon structure, and for providing a voltage output signal proportional to said sensed vertical movement, said voltage output signal providing an indication of angular rotation detected by said gyroscope.

25 2. The gyroscope of claim 1 wherein said lateral vibration of said first and second vibratable structures effects simultaneous vertical movement of said first and second vibratable structures upon the occurrence of angular rotation of said gyroscope about said first rotation sensitive axis.

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3. The system of claim 1 wherein said first and second vibratable structures include first and second open-ended tuning forks; and

5 wherein each of said first and second open-ended tuning forks are suspended over said etched pit by a first end coupled to said silicon substrate.

4. The system of claim 3 wherein each of said first and second tuning forks include a mass disposed proximate a second end of each of said first and second tuning forks, said mass and said second end of each of said first and second tuning forks suspended over said etched pit.

5. The gyroscope of claim 1 wherein said first and second vibratable structures include first and second closed-ended vibratable structures.

15 6. The gyroscope of claim 5 wherein said first closed-ended vibratable structure includes a first end coupled to a first region of said silicon substrate, and a second end coupled to a second region of said silicon substrate, said second region located generally diametrically opposed from said first region; and

20 said second closed-ended vibratable structure is disposed parallel to said first closed-ended vibratable structure, and includes a first end coupled to a first region of said silicon substrate, and a second end coupled to a second region of said silicon substrate, said second region located generally diametrically opposed from said first region.

25 7. The gyroscope of claim 6 wherein each of said first and second closed-ended vibratable structures include a mass disposed generally about a longitudinal central point of each of said first and second closed-ended vibratable structures.

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8. The gyroscope of claim 7 wherein each of said mass include a silicon mass on which is disposed a counter weight.

9. The gyroscope of claim 8 wherein said counter weight is selected from the high density group including gold tungsten and lead.

10. The gyroscope of claim 8 wherein each of said silicon masses is integral with said first and second vibratable structures respectively.

11. The gyroscope of claim 7 wherein said mass on each of said first and second closed-ended vibratable structures includes a center of gravity within said first plane.

12. The gyroscope of claim 5 wherein each of said first and second closed-ended vibratable structures includes:

first and second support beams, each of said first and second support beams including a first end coupled to a first region of said silicon substrate, and a second end coupled to a first region of said mass; and

third and fourth support beams, each of said third and fourth support beams including a first end coupled to a second region of said silicon substrate, and a second end coupled to a second region of said mass, said second region of said mass and said second region of said silicon substrate located generally diametrically opposed from said first region of said mass and said first region of said silicon substrate respectively.

13. The gyroscope of claim 12 wherein each of said support beams include first and second portions, said first portion proximate said first end and coupled to said silicon substrate; and

said second portion disposed proximate said second end and coupled to said mass.

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14. The gyroscope of claim 13 wherein each of said second portion of each of said support beams includes a height-to-width ratio which is greater than the height-to-width ratio of each of said first portions of each of said support beams.

5 15. The gyroscope of claim 14 wherein the height-to-width ratio of each of said first portion of each of said support beams is selected from the range of .1 to 1.

10 16. The gyroscope of claim 14 wherein the height-to-width ratio of each of said second portion of each of said support beams is selected from the range of 1-10.

17. The gyroscope of claim 1 further including:

15 first and second flexible elements coupling said non-etched silicon structure to said substrate, and suspending said non-etched silicon structure over the selectively etched pit, each of said flexible elements integral with said substrate and said non-etched silicon structure, and disposed generally co-linear and co-planar with said first rotation sensitive axis, for allowing said non-etched silicon structure to rotate about said first rotation sensitive axis;

20 said first flexible element including a first end coupled to a first region of said silicon substrate and a second end coupled to a first side of said non-etched silicon structure;

25 said second flexible element including a first end coupled to a second region of said silicon substrate diametrically opposed from said first region of said silicon substrate and said first flexible element, and a second end coupled to a second side of said non-etched silicon structure;

30 said non-etched silicon structure including first and second segments, said first segment structurally coupled and electrically isolated from said second segment;

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said first vibratable structure including a first end coupled to a first region of said first segment, and a second end coupled to a second region of said first segment, said second region located generally diametrically opposed from said first region;

said second vibratable structure including a first end coupled to a first region of said second segment, and a second end coupled to a second region of said second segment, said second region located generally diametrically opposed from said first region;

wherein said drive means is operative for energizing said first and second vibratable structures to vibrate laterally, co-planar with and along an axis normal to said first rotation sensitive axis, said vibrating of said first and second vibratable structures effecting rotational movement of said non-etched silicon structure about said rotation sensitive axis upon the occurrence of angular rotation of said gyroscope about said first rotation sensitive axis; and

wherein said means for sensing senses rotation of said non-etched silicon structure, for providing a voltage output signal proportional to the rotational movement of said non-etched silicon structure, said voltage output signal providing an indication of angular rotation detected by said gyroscope.

18. The gyroscope of claim 17 further including means for providing stress relief of tensile forces between said non-etched silicon structure and said silicon substrate.

19. The gyroscope of claim 18 wherein said means for providing stress relief includes at least one tension relief beam formed by an opening having a predetermined length and width disposed in said non-etched silicon structure, said at least one tension relief beam coupled to the second end of at least one of said first and second flexible elements.

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20. The gyroscope of claim 19 further including a second opening having a predetermined length and width, and forming a second tension relief beam to which is coupled the second end of the other of said first and second flexible elements.

5 21. The gyroscope of claim 19 wherein said at least one tension relief beam has a high height-to-width ratio.

22. The gyroscope of claim 21 wherein said height-to-width ratio is at least two-to-one.

10 23. The gyroscope of claim 17 wherein said first and second segments are structurally coupled and electrically isolated by means of a lap joint.

24. The gyroscope of claim 17 wherein said first and second segment are structurally coupled and electrically isolated by means of a dielectric isolation region.

15 25. The gyroscope of claim 1 wherein said drive means applies a sinusoidal voltage to each of said first and second vibratable structures.

20 26. The gyroscope of claim 25 wherein said sinusoidal voltage applied at a given instant to said first vibratable structure is of opposite polarity to the sinusoidal voltage applied at said given instant to said second vibratable structure.

27. The gyroscope of claim 1 wherein said means for sensing rotation includes at least one sense electrode.

25 28. The gyroscope of claim 27 wherein said at least one sense electrode includes at least one bridge electrode coupled to said silicon substrate.

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29. The gyroscope of claim 28 wherein said at least one bridge electrode is electrically isolated from said silicon substrate.

5 30. The gyroscope of claim 27 wherein said at least one sense electrode includes at least one buried electrode.

31. The gyroscope of claim 1 wherein said means for sensing rotation includes electrostatic sense means, for electrostatically sensing rotation of said non-etched silicon structure.

10 32. The gyroscope of claim 31 wherein said electrostatic sense means includes means for measuring differential capacitance between said first and second segments of said non-etched silicon structure and at least one sense electrode.

15 33. The gyroscope of claim 14 wherein said first and second segments include regions having a lower mass than the remainder of said first and second segments.

34. The gyroscope of claim 33 wherein said regions of lower mass are constructed of a waffle type construction.

20 35. The gyroscope of claim 1 wherein said silicon substrate further includes a second selectively etched pit over which is suspended a second, non-etched silicon structure, said second, non-etched silicon structure including third and fourth vibratable structures, for forming at least a second,
25 monolithic, micromechanical tuning fork gyroscope disposed co-planar with a first micromechanical tuning fork gyroscope, and oriented co-planar with and orthogonal to said first tuning fork gyroscope, for detecting angular rotation about a second rotation sensitive axis co-planar with and generally
30 orthogonal to said first rotation sensitive axis.

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36. The gyroscope of claim 35 further including a third, monolithic, micromechanical tuning fork gyroscope disposed in a plane orthogonal to said first plane, for detecting angular rotation about a third rotation sensitive axis orthogonal to said first and second rotation sensitive axes.

37. The gyroscope of claim 35 further including

a third gyroscope having a third rotation sensitive axis normal to the plane of the first and second tuning fork gyroscopes and orthogonal to the rotation sensitive axes of the first and second tuning fork gyroscopes; and

first, second and third accelerometers, for detecting acceleration along said first, second and third rotation sensitive axes respectively, and forming along with said first, second and third gyroscopes a three axis instrument measurement unit on one silicon substrate.

38. The gyroscope of claim 1 wherein said drive means includes electromagnetic drive means.

39. The gyroscope of claim 1 wherein said drive means includes electrostatic drive means.

40. The gyroscope of claim 39 wherein said drive means includes at least first and second electrodes, for applying a drive voltage to said first and second vibratable structures.

41. A pivoting, monolithic, micromechanical tuning fork gyroscope, for detecting angular rotation about at least a first rotation sensitive axis, comprising:

a silicon substrate in which has been selectively etched a pit, and over which is suspended a non-etched silicon structure;

first and second flexible elements coupling said non-etched silicon structure to said substrate, and suspending

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said non-etched silicon structure over the selectively etched pit, each of said flexible elements integral with said substrate and said non-etched silicon structure, and disposed generally co-linear and co-planar with said rotation sensitive axis, for allowing said non-etched silicon structure to rotate about said rotation sensitive axis;

said first flexible element including a first end coupled to a first region of said silicon substrate and a second end coupled to a first side of said non-etched silicon structure;

said second flexible element including a first end coupled to a second region of said silicon substrate diametrically opposed from said first region of said silicon substrate, and a second end coupled to a second side of said non-etched silicon structure, diametrically opposed from said first side of said non-etched silicon structure;

said non-etched silicon structure including first and second vibratable structures, said first and second vibratable structures disposed generally parallel to one another, each of said first and second vibratable structures including a mass integral with an associated vibratable structure;

said first vibratable structure including a first end coupled to a first region of said non-etched silicon structure, and a second end coupled to a second region of said non-etched silicon structure, said second region located generally diametrically opposed from said first region;

said second vibratable structure including a first end coupled to a third region of said non-etched silicon structure, and a second end coupled to a fourth region of said non-etched silicon structure, said fourth region located generally diametrically opposed from said third region;

drive means, operative for energizing said first and second vibratable structures to vibrate along an axis coplanar with and normal to said rotation sensitive axis, vibration of said first and second vibratable structures

- 40 -

effecting rotational movement of said non-etched silicon structure about said rotation sensitive axis upon the occurrence of angular rotation of said gyroscope about said first rotation sensitive axis; and

5 means for sensing rotation of said non-etched silicon structure, and for providing a voltage output signal proportional to the rotational movement of said non-etched silicon structure, said voltage output signal providing an indication of angular rotation detected by said gyroscope.

10 42. A pivoting, monolithic, micromechanical tuning fork gyroscope, for detecting angular rotation about at least a first rotation sensitive axis, comprising:

a silicon substrate in which has been selectively etched a pit, and over which is suspended a non-etched silicon structure;

15 first and second flexible elements coupling said non-etched silicon structure to said substrate, and suspending said non-etched silicon structure over the selectively etched pit, each of said flexible elements integral with said substrate and said non-etched silicon structure, and disposed
20 generally co-linear with said rotation sensitive axis, for allowing said non-etched silicon structure to rotate about said rotation sensitive axis;

said first flexible element including a first end
25 coupled to a first region of said silicon substrate and a second end coupled to a first side of said non-etched silicon structure;

said second flexible element including a first end
coupled to a second region of said silicon substrate
30 diametrically opposed from said first region of said silicon substrate and said first flexible element, and a second end coupled to a second side of said non-etched silicon substrate;

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said non-etched silicon structure including first and second segments, said first segment structurally coupled and electrically isolated from said second segment;

5 said non-etched silicon structure further including first and second vibratable structures, said first and second vibratable structures disposed generally parallel to one another, each of said first and second vibratable structures including a mass integral with an associated vibratable structure;

10 said first vibratable structure including a first end coupled to a first region of said first segment, and a second end coupled to a second region of said first segment, said second region located generally diametrically opposed from said first region;

15 said second vibratable structure including a first end coupled to a first region of said second segment, and a second end coupled to a second region of said second segment, said second region located generally diametrically opposed from said first region;

20 drive means, operative for energizing said first and second vibratable structures to vibrate along an axis coplanar with and normal to said rotation sensitive axis, vibration of said first and second vibratable structures effecting rotational movement of said non-etched silicon structure about said rotation sensitive axis upon the
25 occurrence of angular rotation of said gyroscope about said first rotation sensitive axis; and

30 means for sensing rotation of said non-etched silicon structure, and for providing a voltage output signal proportional to the rotational movement of said non-etched silicon structure, for providing an indication of angular rotation detected by said gyroscope.

43. The gyroscope of claim 17 further including rebalance means, responsive to said means for sensing, for
35 counteracting and zeroing the rotational movement of said

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non-etched silicon structure about said rotation sensitive axis upon the occurrence and sensing of angular rotational of said gyroscope about said rotation sensitive axis.

5 44. The gyroscope of claim 41 further including rebalance means, responsive to said means for sensing, for counteracting and zeroing the rotational movement of said non-etched silicon structure about said rotation sensitive axis upon the occurrence and sensing of angular rotational of said gyroscope about said rotation sensitive axis.

10 45. The gyroscope of claim 42 further including rebalance means, responsive to said means for sensing, for counteracting and zeroing the rotational movement of said non-etched silicon structure about said rotation sensitive axis upon the occurrence and sensing of angular rotational
15 of said gyroscope about said rotation sensitive axis.

46. A micromechanical tuning fork gyroscope, for detecting angular rotation about at least a first rotation sensitive axis, comprising:

20 a substrate including a base region over which is suspended an angular rate sensitive structure;

said angular rate sensitive structure disposed within
a first plane and including at least first and second
vibratable structures, said first and second vibratable
structures disposed generally adjacent and parallel to one
25 another;

drive means, for energizing said first and second
vibratable structures to vibrate laterally along an axis
normal to said rotation sensitive axis and within said first
plane, said lateral vibration of said at least first and
30 second vibratable structures effecting simultaneous vertical
movement of at least a portion of said angular rate sensitive
structure in a direction parallel to a second plane normal
to said first plane upon the occurrence of angular rotation

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of said gyroscope about said first rotation sensitive axis;
and

means for sensing said simultaneous vertical movement
of said at least a portion of said angular rate sensitive
structure, for providing a voltage output signal proportional
to said sensed simultaneous vertical movement, said voltage
output signal providing an indication of an amount of angular
rotation detected by said gyroscope.

47. The gyroscope of claim 46 wherein said first and second
vibratable structures include first and second open-ended
tuning forks; and

wherein each of said first and second open-ended tuning
forks are coupled proximate a first end and suspended over
said base region by said first end which is coupled to said
substrate.

48. The gyroscope of claim 46 wherein said first and second
vibratable structures include first and second closed-ended
vibratable structures;

wherein said first closed-ended vibratable structure
includes a first end coupled to a first region of said
substrate, and a second end coupled to a second region of
said substrate, said second region located generally
diametrically opposed from said first region; and

wherein said second closed-ended vibratable structure
is disposed parallel to said first closed-ended vibratable
structure, and includes a first end coupled to said first
region of said substrate, and a second end coupled to said
second region of said substrate.

49. The gyroscope of claim 48 wherein each of said first and
second closed-ended vibratable structures include a mass
disposed generally about a longitudinal central point of each
of said first and second closed-ended vibratable structures.

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50. The gyroscope of claim 46 further including:

5 first and second flexible elements coupling said angular rate sensitive structure to said substrate, and suspending said angular rate sensitive structure over the base of said substrate, each of said flexible elements integral with said substrate and said angular rate sensitive structure, and disposed generally co-linear and co-planar with said first rotation sensitive axis, for allowing said angular rate sensitive structure to rotate about said first rotation sensitive axis;

10 said first flexible element including a first end coupled to a first region of said substrate and a second end coupled to a first side of said angular rate sensitive structure;

15 said second flexible element including a first end coupled to a second region of said substrate diametrically opposed from said first region of said substrate and said first flexible element, and a second end coupled to a second side of said angular rate sensitive structure;

20 said angular rate sensitive structure including first and second segments, said first segment structurally coupled and electrically isolated from said second segment;

25 said first vibratable structure including a first end coupled to a first region of said first segment, and a second end coupled to a second region of said first segment, said second region located generally diametrically opposed from said first region;

30 said second vibratable structure including a first end coupled to a first region of said second segment, and a second end coupled to a second region of said second segment, said second region located generally diametrically opposed from said first region;

35 wherein said drive means is operative for energizing said first and second vibratable structures to vibrate laterally, co-planar with and along an axis normal to said first rotation sensitive axis, said vibrating of said first

- 45 -

and second vibratable structures effecting rotational movement of said angular rate sensitive structure about said first and second flexible elements and rotation sensitive axis, upon the occurrence of angular rotation of said gyroscope about said first rotation sensitive axis; and

wherein said means for sensing senses rotation of said angular rate sensitive structure, for providing a voltage output signal proportional to the sensed rotational movement of said angular rate sensitive structure, said voltage output signal providing an indication of an amount of angular rotation detected by said gyroscope.

51. The gyroscope of claim 46 wherein said gyroscope includes a surface machined micromechanical angular rate sensor; and

wherein said substrate and said angular rate sensitive structure comprise polysilicon.

52. The gyroscope of claim 46 wherein said substrate includes at least first and second layers, said first layer including said substrate base region said second layer disposed over said first layer and including said angular rate sensitive structure suspended over said substrate base region.

53. The gyroscope of claim 52 wherein said substrate further includes a third layer disposed over said second layer, said third layer including at least one electrode disposed above said angular rate sensitive structure for sensing vertical movement of said angular rate sensitive structure.

54. A micromechanical tuning fork gyroscope, for detecting angular rotation about at least a first rotation sensitive axis, comprising:

a frame from which is suspended an angular rate sensitive structure;

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said angular rate sensitive structure being aligned with a first plane and including at least first and second vibratable structures, said first and second vibratable structures disposed generally adjacent and parallel to one another;

flexible linkage supporting said frame from a platform; drive means, for energizing said first and second vibratable structures to vibrate laterally along an axis normal to said rotation sensitive axis and within said first plane, said lateral vibration of said at least first and second vibratable structures effecting rotation of said frame about said first axis in response to angular rotation of said gyroscope about said first rotation sensitive axis; and

means for providing a voltage output signal proportional to said frame rotation, said voltage output signal providing an indication of an amount of angular rotation detected by said gyroscope.

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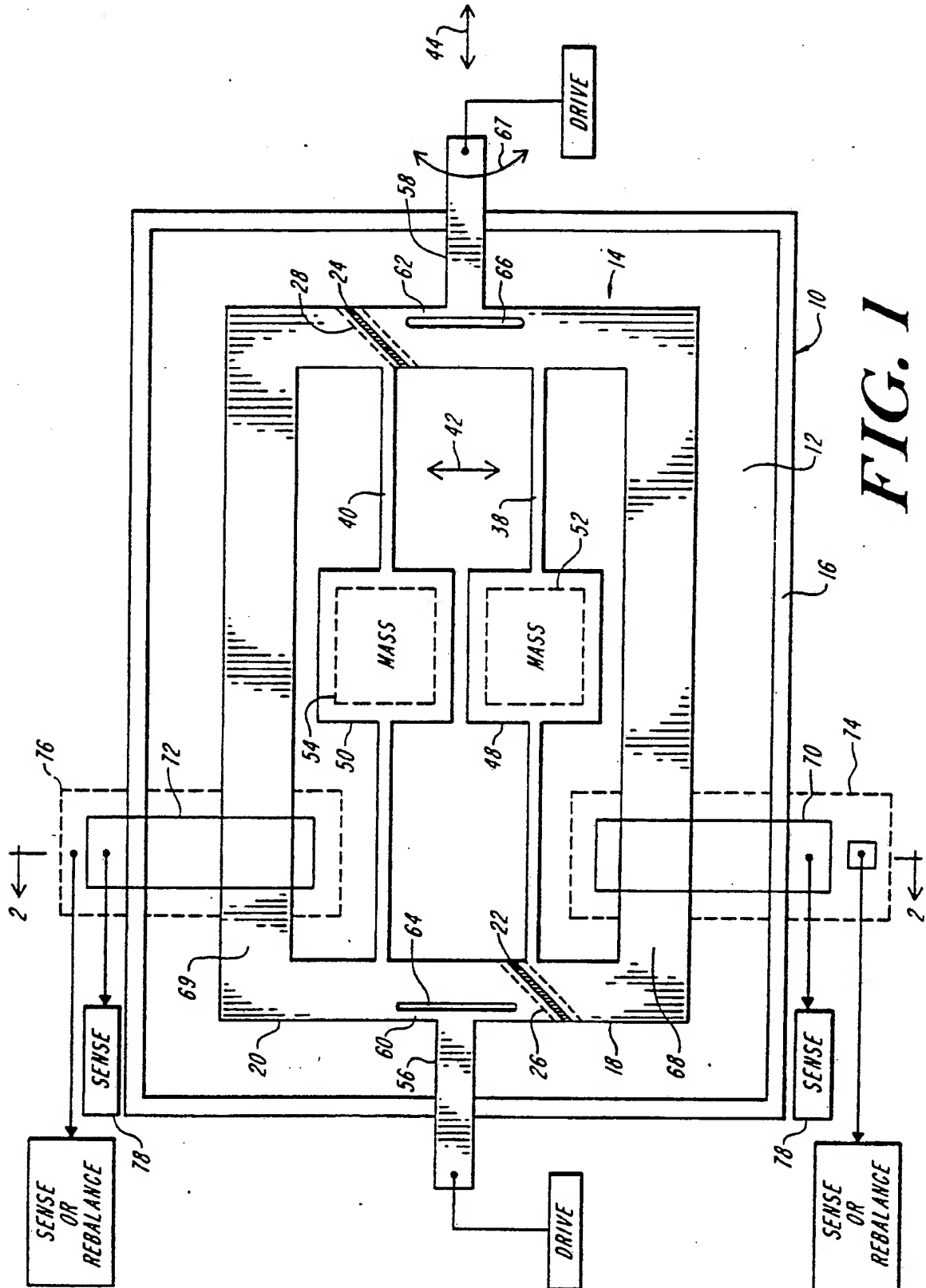


FIG. 1

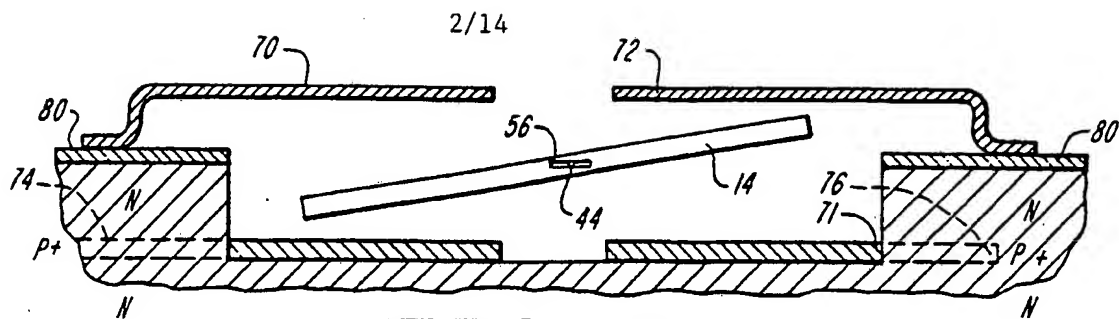


FIG. 2

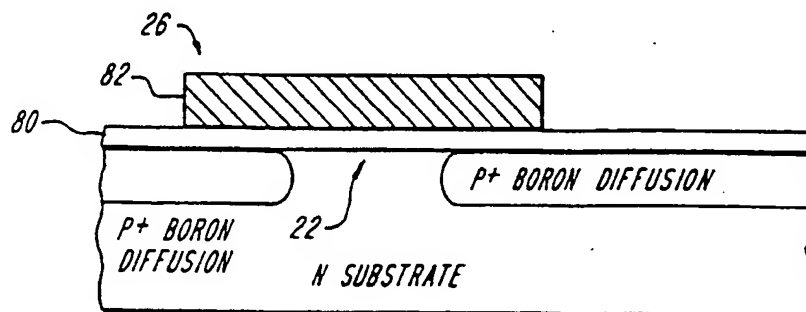


FIG. 3

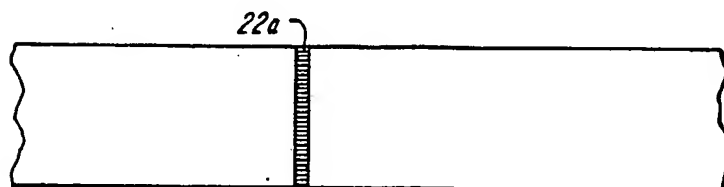


FIG. 4A

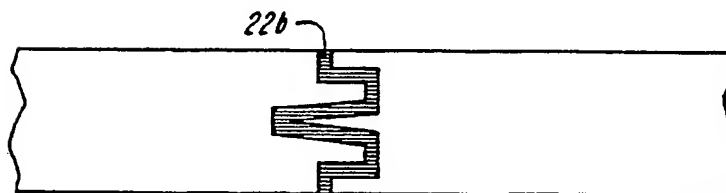
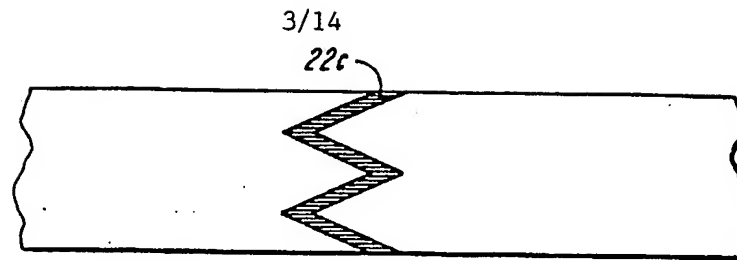
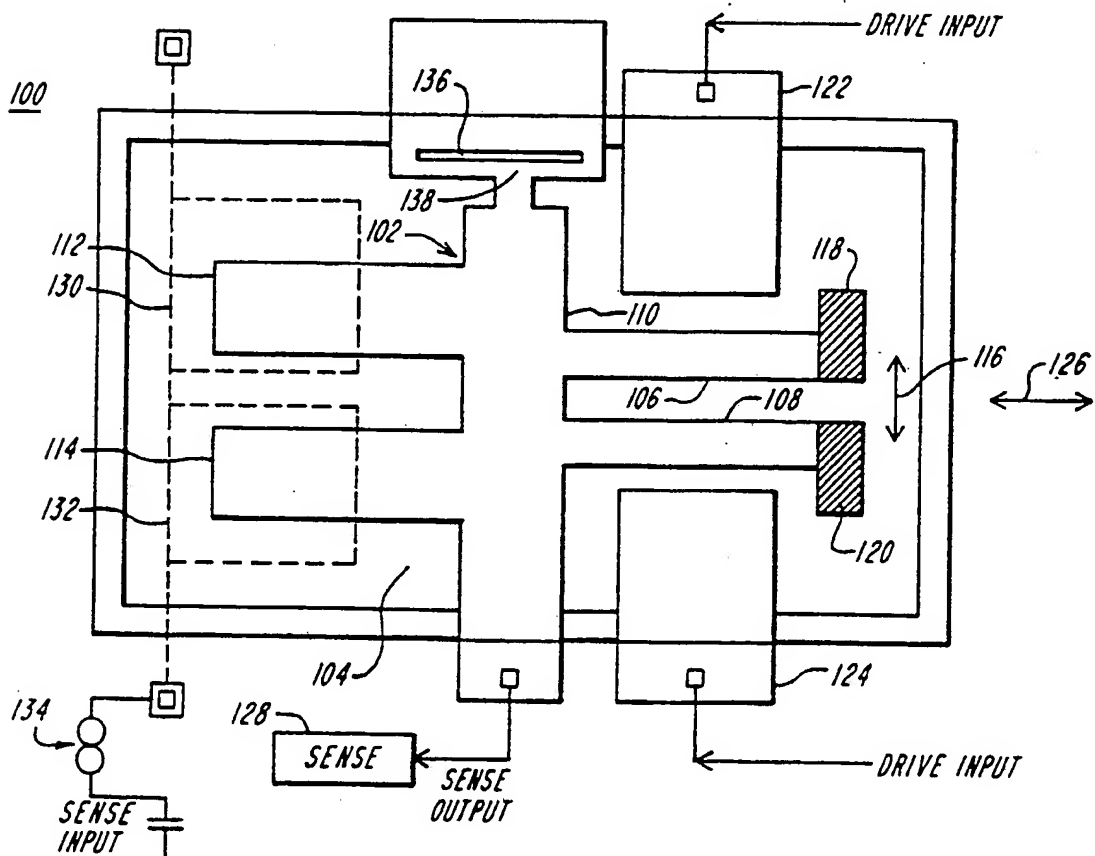


FIG. 4B

**FIG. 4C****FIG. 5**

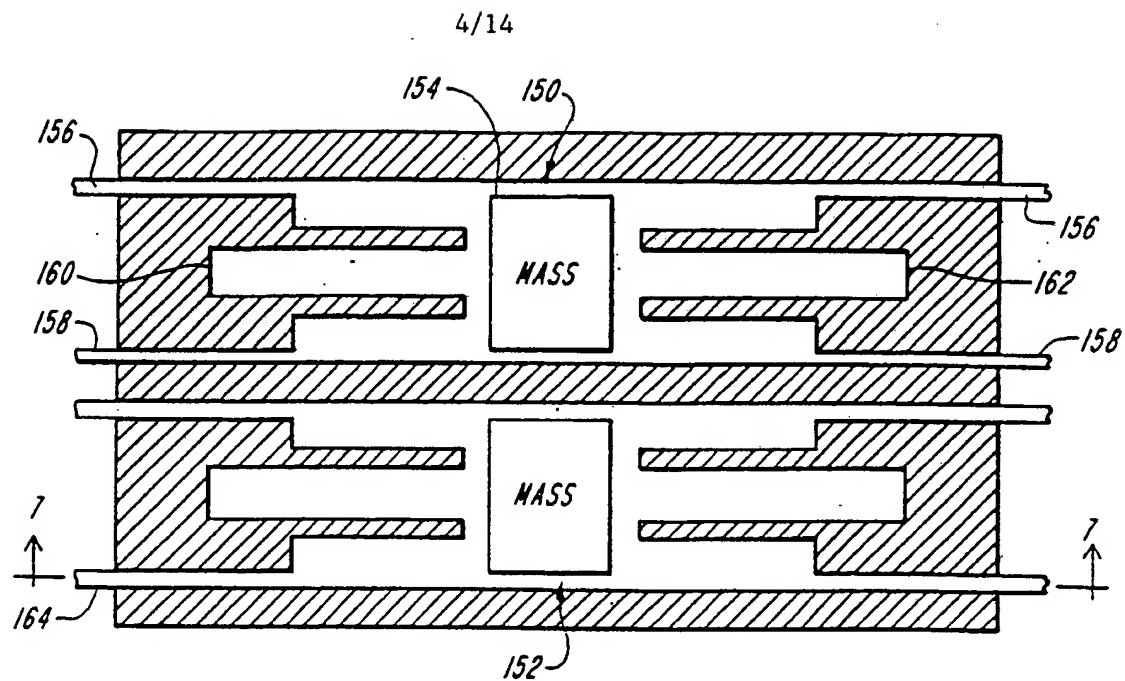


FIG. 6

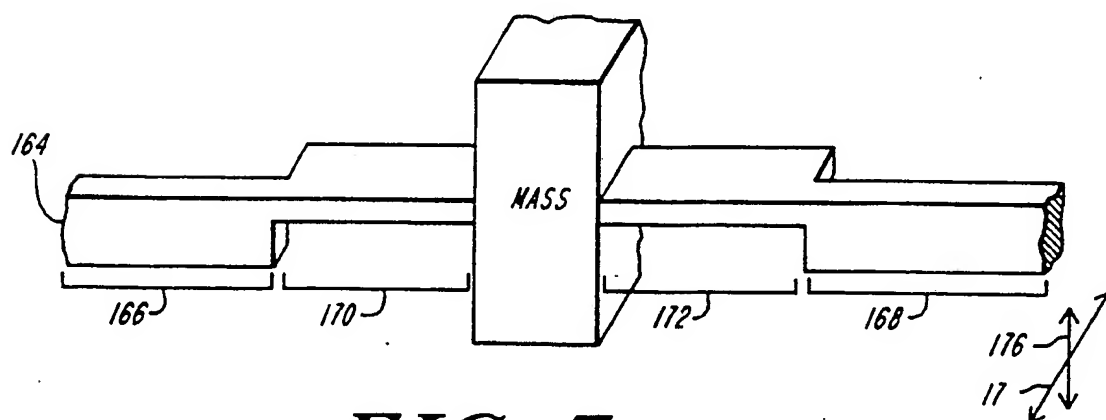


FIG. 7

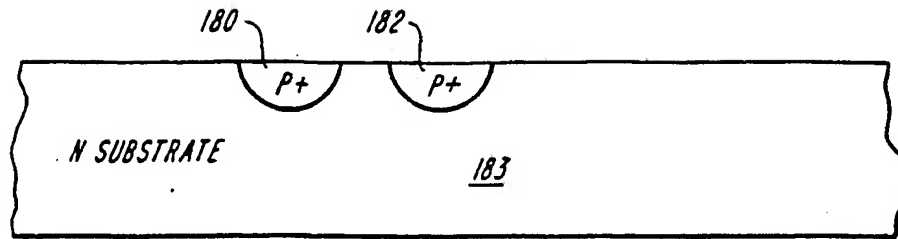


FIG. 8A

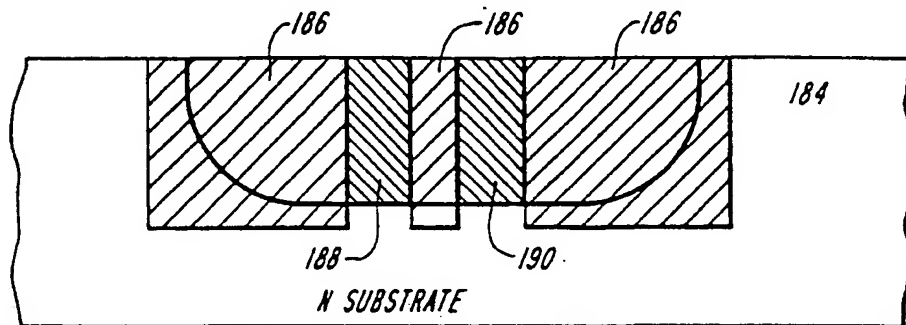


FIG. 8B

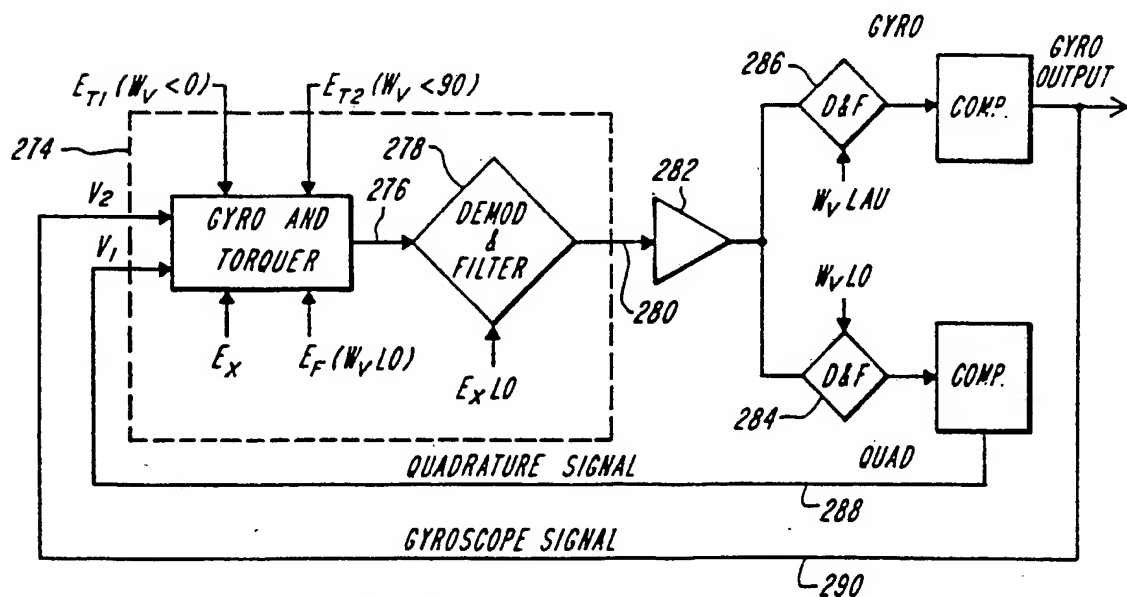
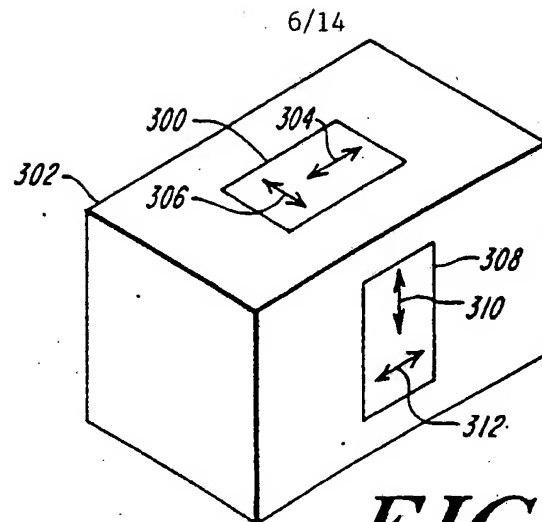
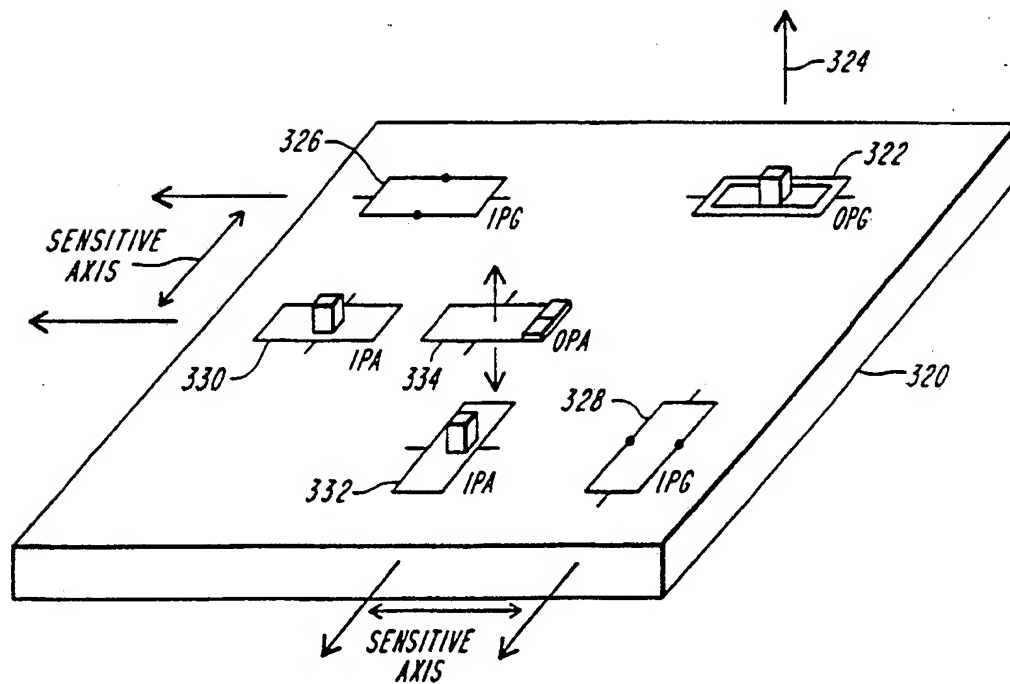


FIG. 15

**FIG. 9A**

ALL INSTRUMENTS WILL HAVE THEIR OWN BUFFER AMPLIFIER

IPG - IN PLANE GYRO

OPG - OUT OF PLANE GYRO (CURRENT INSTRUMENT)

IPA - IN PLANE ACCELEROMETER (COULD ALSO USE VIBRATORY STRING TYPE)

OPA - OUT OF PLANE ACCELEROMETER (CURRENT INSTRUMENT)

FIG. 9B

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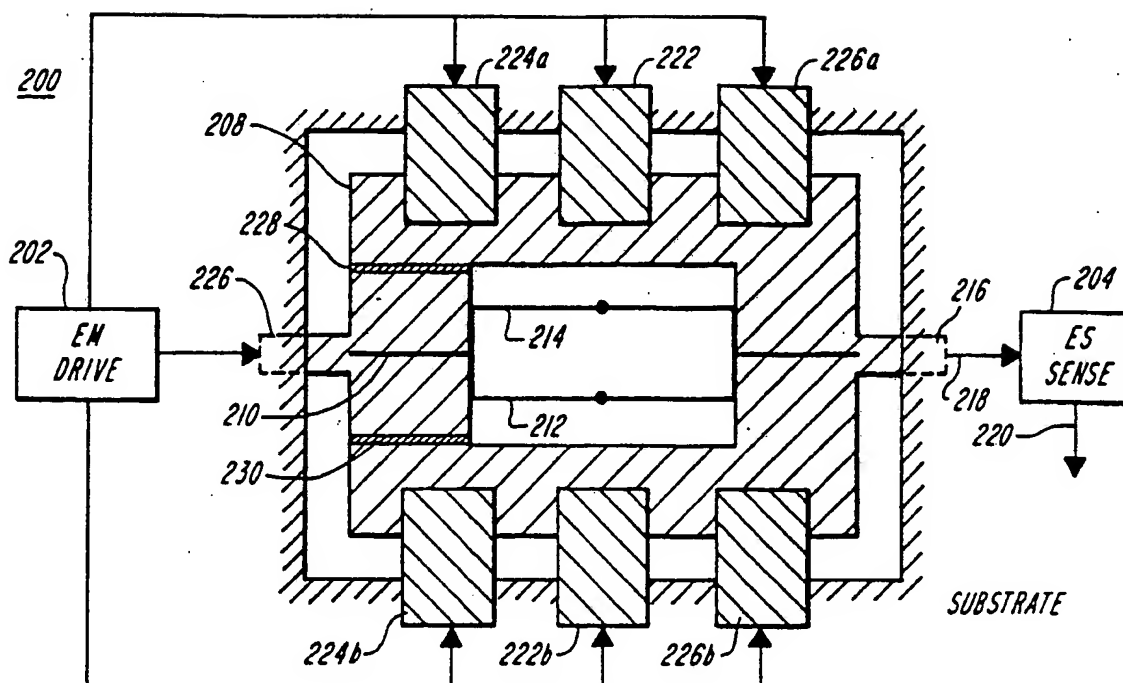


FIG. 10

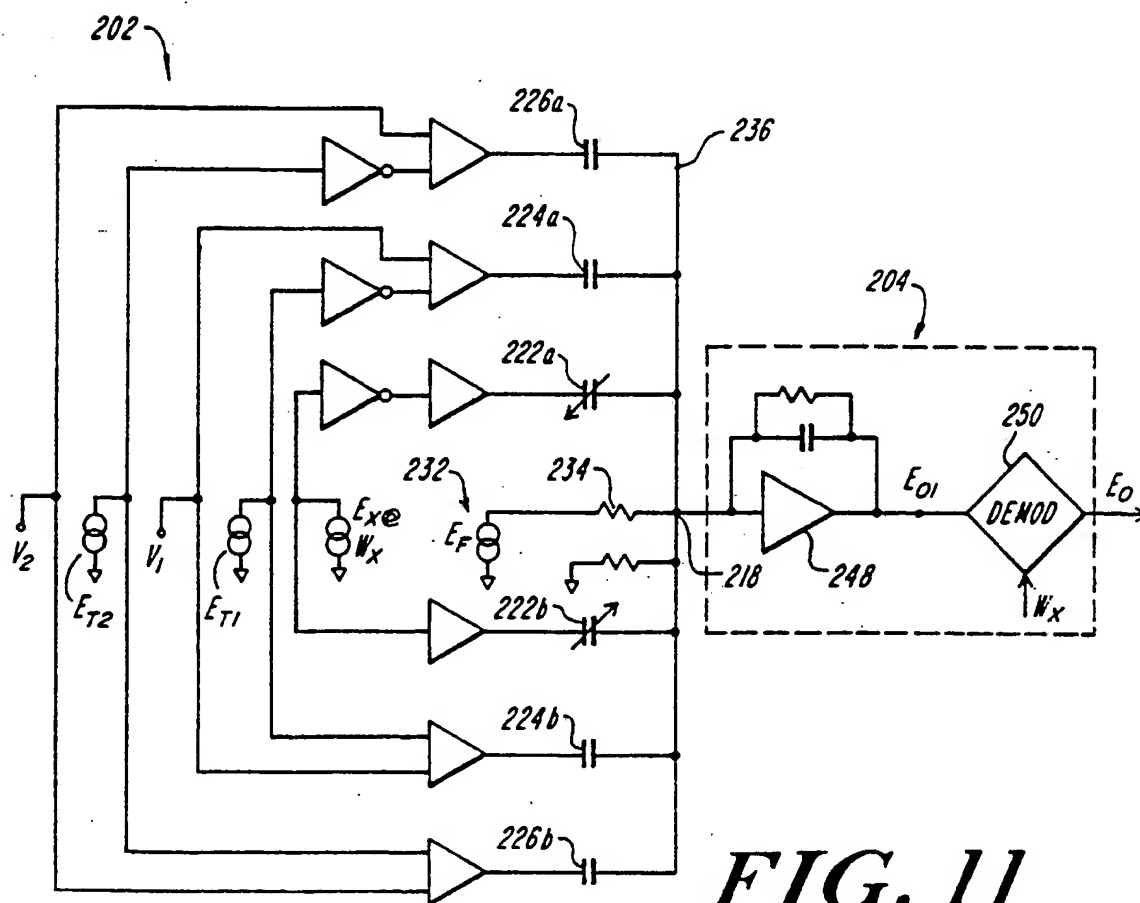


FIG. 11

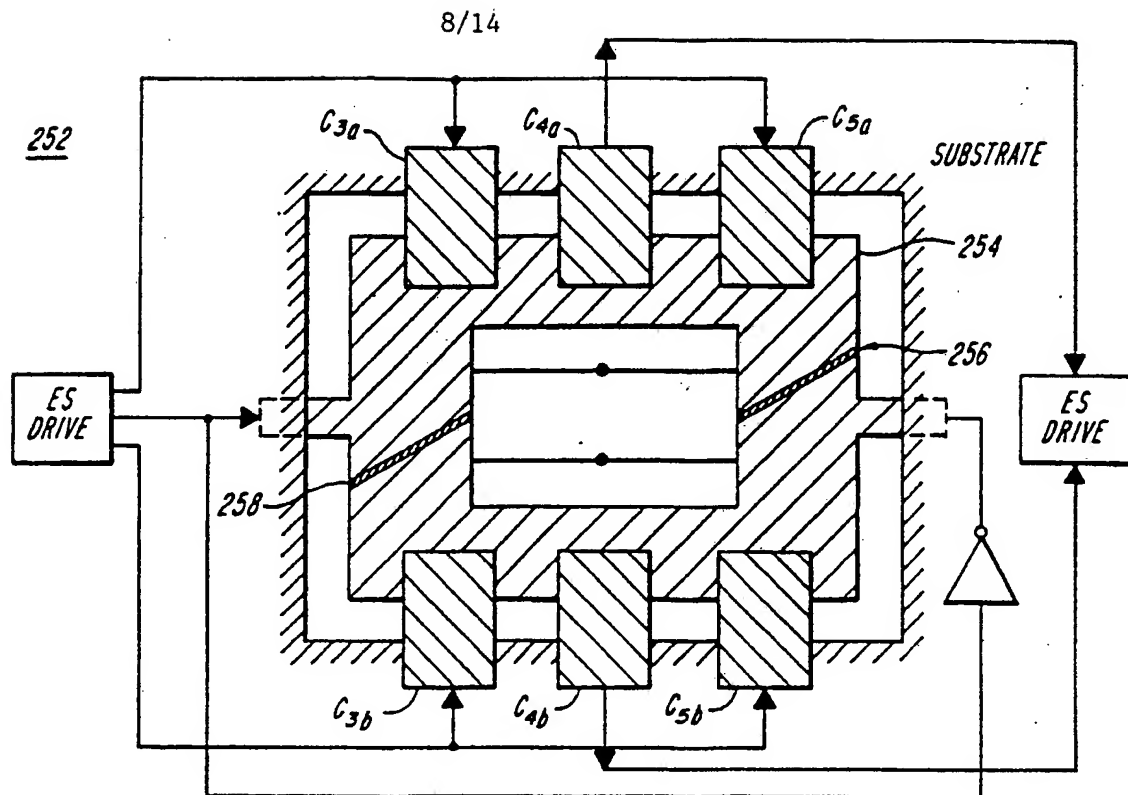


FIG. 12

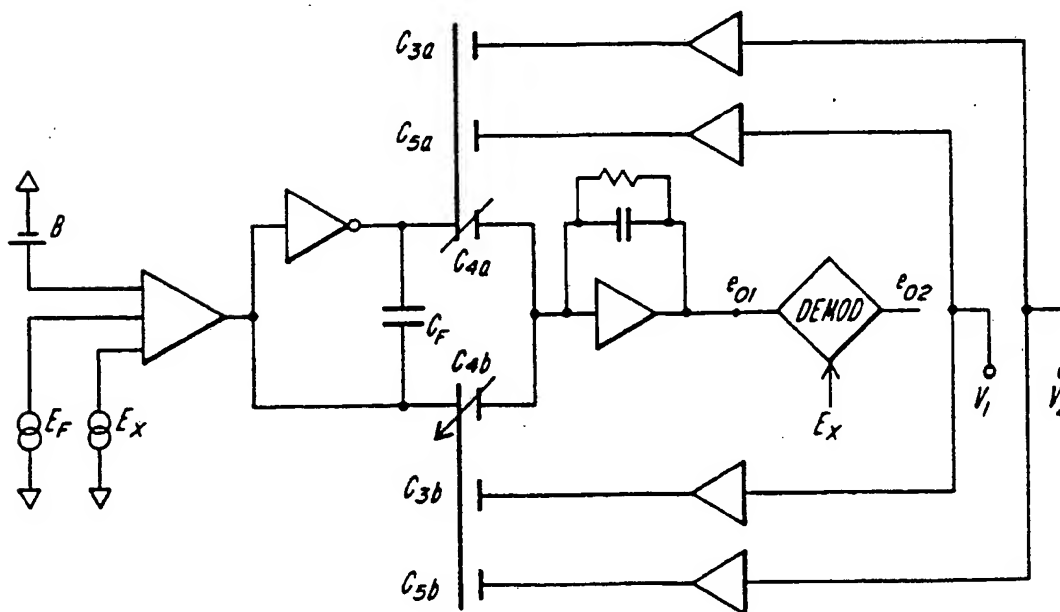
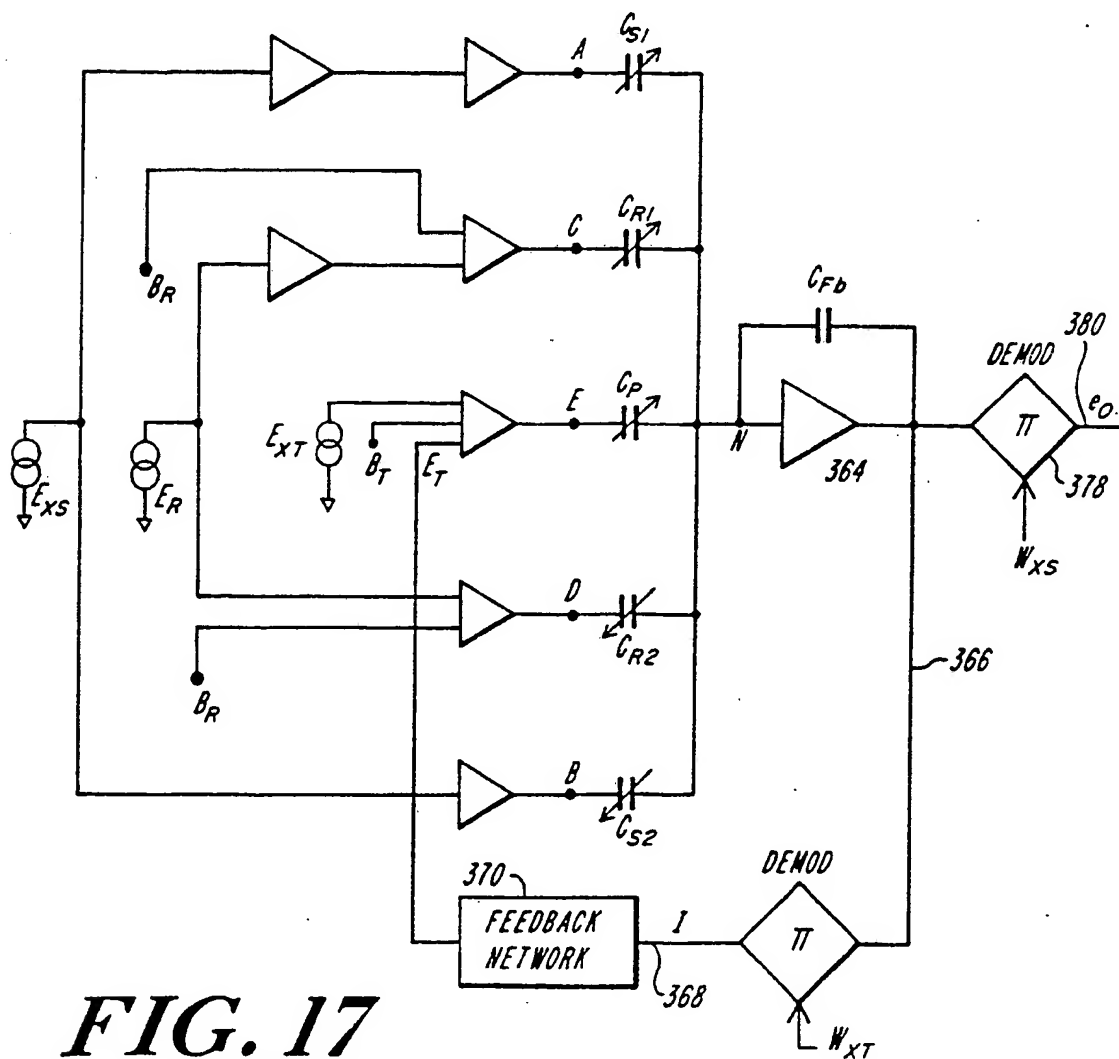
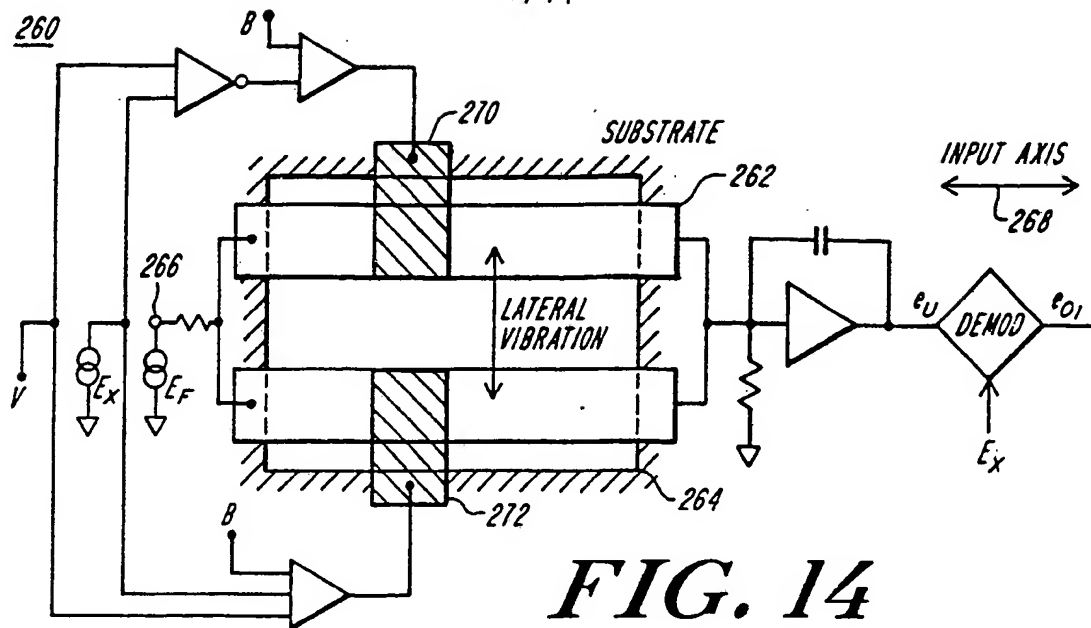


FIG. 13

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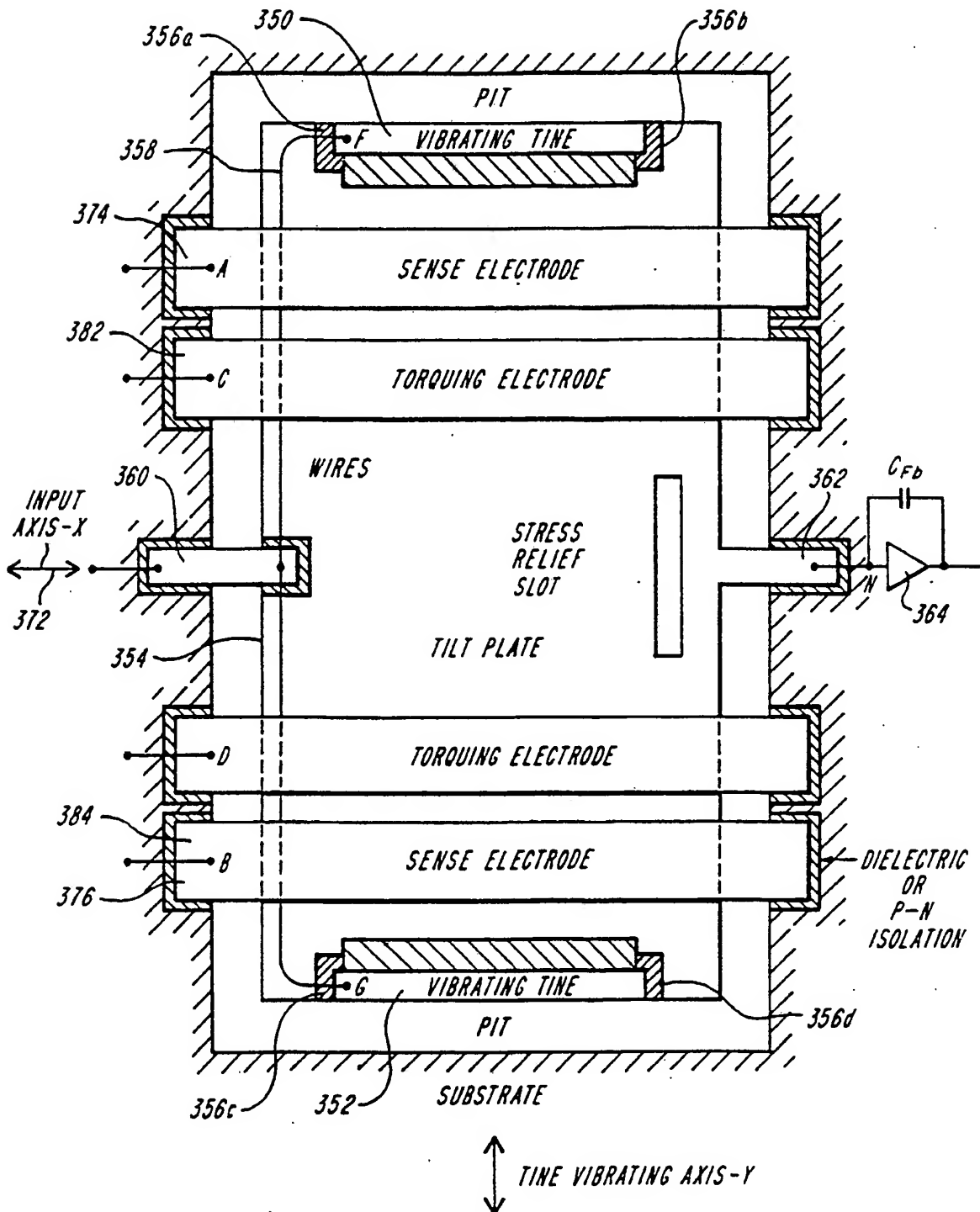


FIG. 16

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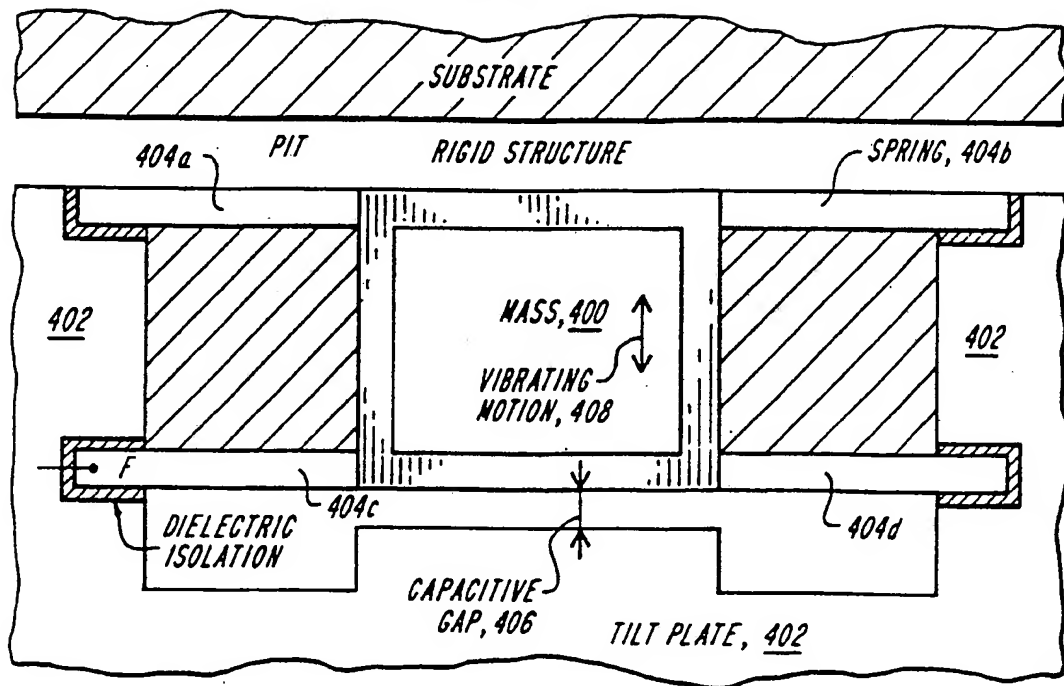


FIG. 18

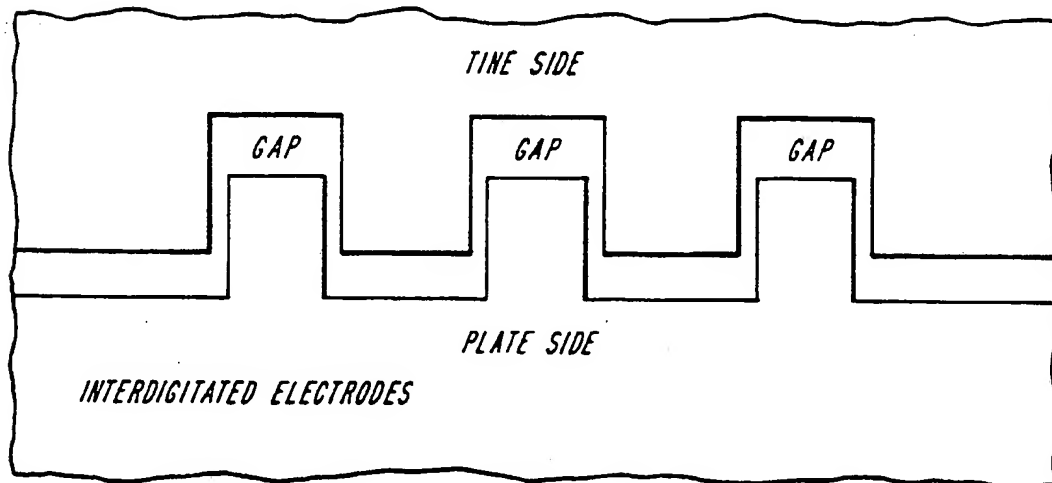


FIG. 19

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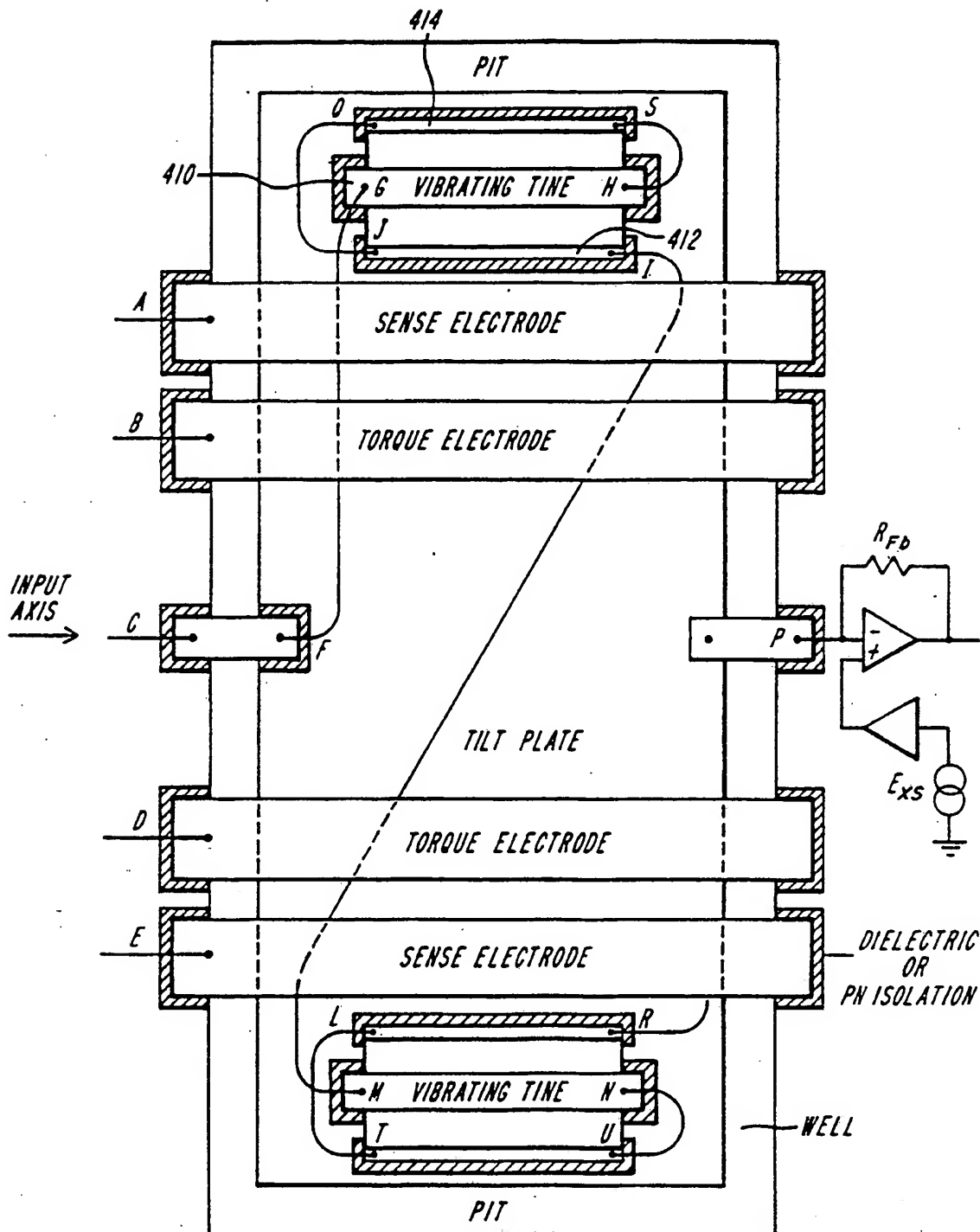


FIG. 20

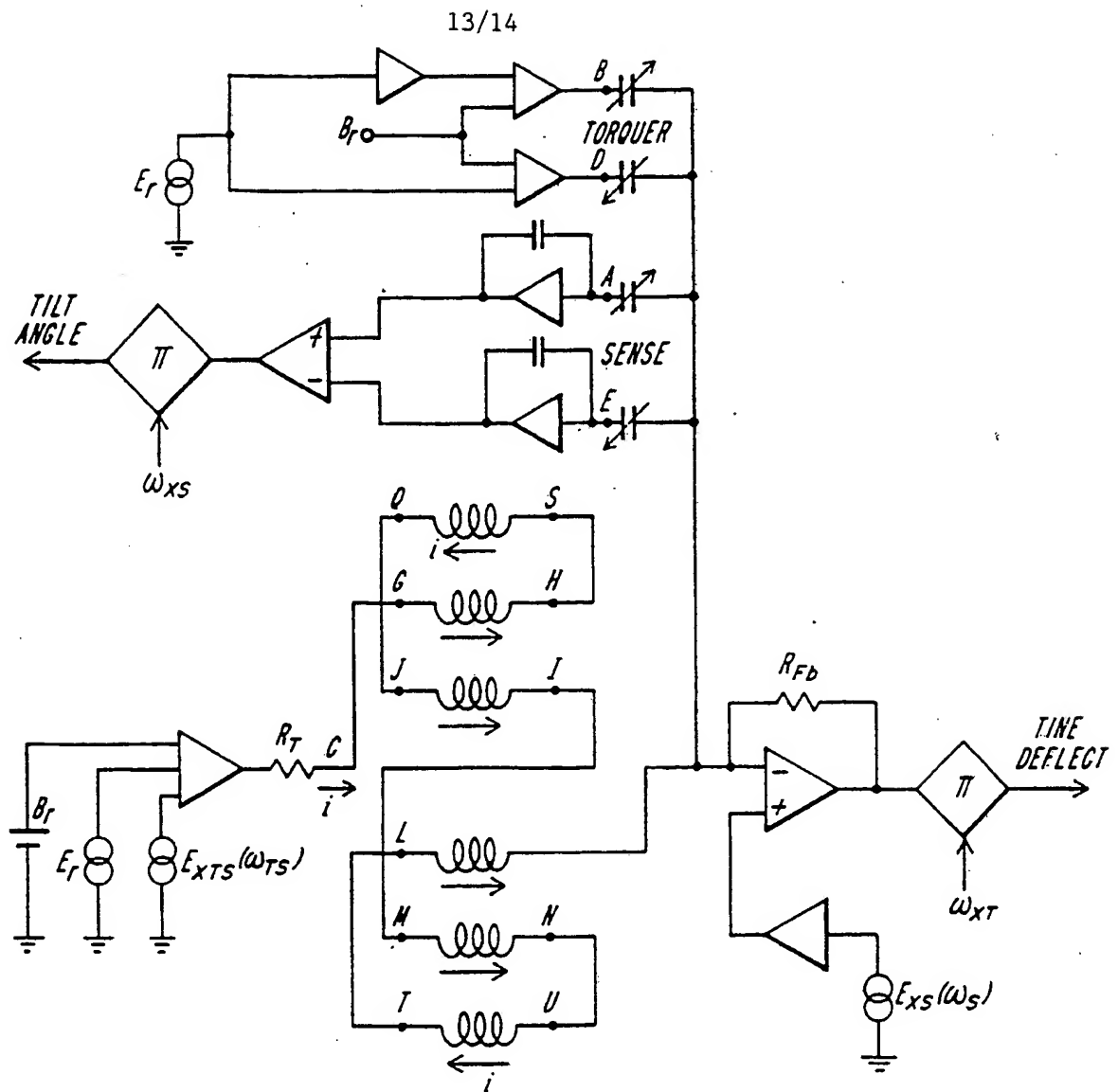


FIG. 21

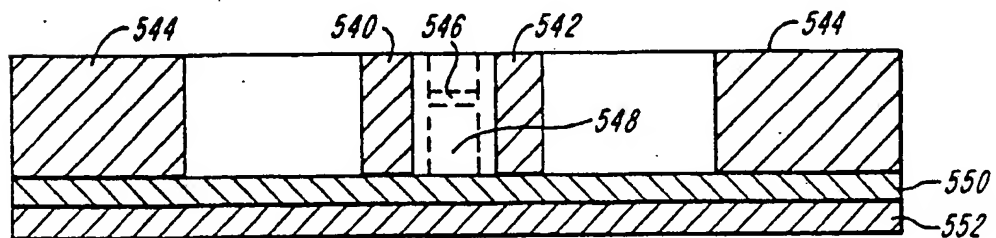


FIG. 24

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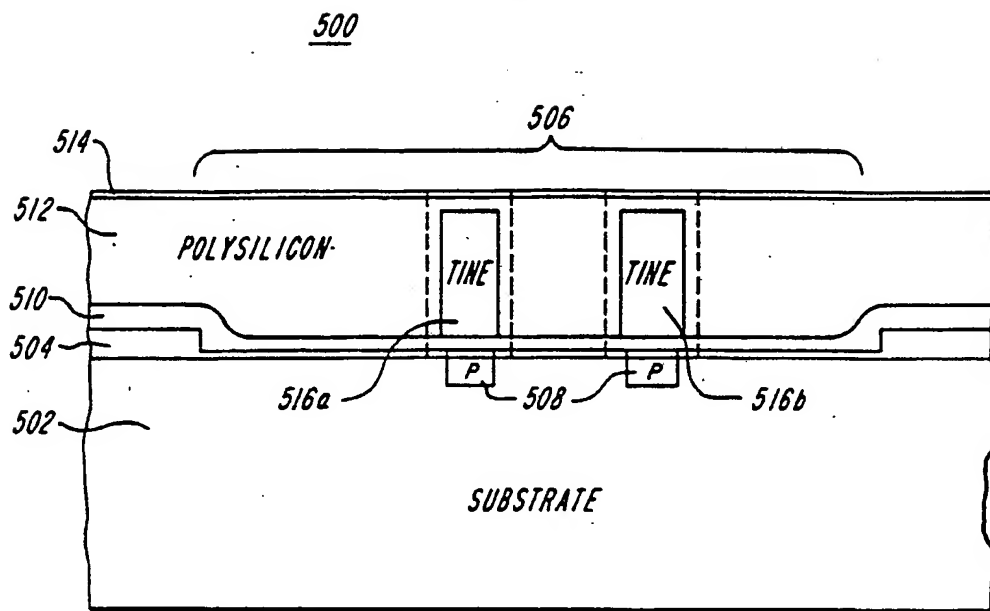


FIG. 22

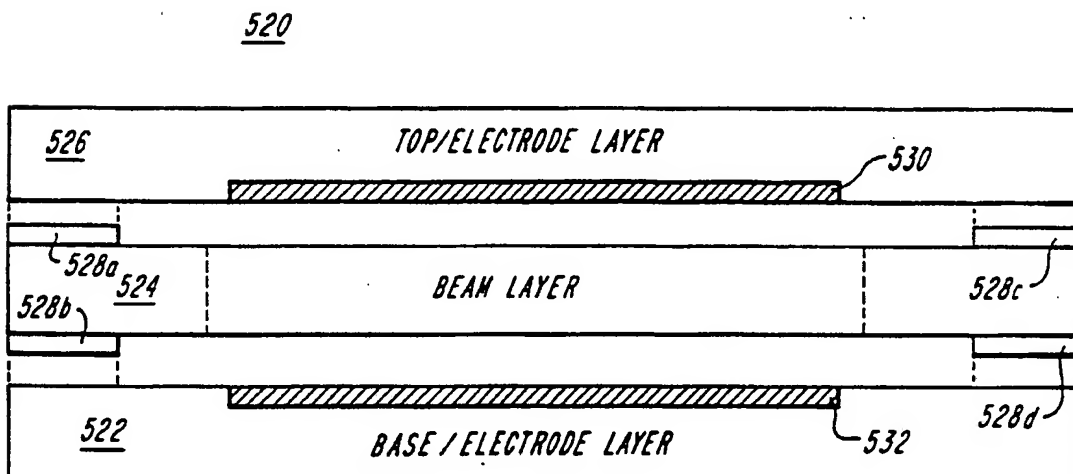


FIG. 23

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US92/07685

A. CLASSIFICATION OF SUBJECT MATTER

IPC(5) :G01P 9/04

US CL :73/505,510

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

U.S. : 73/505,510

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X/Y	US, A, 4,654,663 (Alsenz) 31 March 1987, see entire document	1 - 6 , 1 7 , 2 4 - 27,31,32,41,42,46- 48,50-54/28-30,35-- 40,43-45
Y	US, A, 5,016,072 (Greiff) 14 May 1991 See fig. 1 and col. 4, line 46 to col. 5 line 38.	28-30, 39,40, 43-45
Y	US, A, 5,038,613 (Takenaka et al) 13 August 1991 see figure 8	35-37
Y	US, A, 4,342,227 (Petersen et al) 03 August 1982 see fig. 1	35-37
Y	US, A, 4,674,331 (Watson) 23 June 1987 see fig. 8	38
X	US, A, 3,251,231 (Hunt et al) 17 May 1966 see fig. 4	54

☐ Further documents are listed in the continuation of Box C. ☐ See patent family annex.

* Special categories of cited documents:	*T	later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
A document defining the general state of the art which is not considered to be part of particular relevance	*X*	document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
E earlier document published on or after the international filing date	*Y*	document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
L document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	*G*	document member of the same patent family
O document referring to an oral disclosure, use, exhibition or other means		
P document published prior to the international filing date but later than the priority date claimed		

Date of the actual completion of the international search 11 NOVEMBER 1992	Date of mailing of the international search report 28 DEC 1992
Name and mailing address of the ISA/ Commissioner of Patents and Trademarks Box PCT Washington, D.C. 20231	Authorized officer JOHN CHAPMAN
Facsimile No. NOT APPLICABLE	Telephone No. (703) 305-4920

INTERNATIONAL SEARCH REPORT

International application No.

PCT/US92/07685

Box I Observations where certain claims were found unsearchable (Continuation of item 1 of first sheet)

This international report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:

1. ☐ Claims Nos.:
because they relate to subject matter not required to be searched by this Authority, namely:

2. ☐ Claims Nos.:
because they relate to parts of the international application that do not comply with the prescribed requirements to such an extent that no meaningful international search can be carried out, specifically:

3. ☐ Claims Nos.:
because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).

Box II Observations where unity of invention is lacking (Continuation of item 2 of first sheet)

This International Searching Authority found multiple inventions in this international application, as follows:
Please See Extra Sheet.

1. ☒ As all required additional search fees were timely paid by the applicant, this international search report covers all searchable claims. (Telephone Practice)
2. ☐ As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.
3. ☐ As only some of the required additional search fees were timely paid by the applicant, this international search report covers only those claims for which fees were paid, specifically claims Nos.:

4. ☐ No required additional search fees were timely paid by the applicant. Consequently, this international search report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.:

Remark on Protest

- ☐ The additional search fees were accompanied by the applicant's protest.
☐ No protest accompanied the payment of additional search fees.

BOX II. OBSERVATIONS WHERE UNITY OF INVENTION WAS LACKING

This ISA found multiple inventions as follows:

Group I. That species comprising an open-ended tuning fork as shown in fig. 5: Claims 3,4 and 47.

Group II. That species comprising a pivoting, closed-ended tuning fork as shown in fig. 1.: Claims 6-16,33 and 34.

Group III. That species comprising a non-pivoting, closed-ended tuning fork as shown in fig. 6: Claims 17-24,38,41-45,50 and 54.

Claims 1,2,25-32,35-37,39,40 and 46,51-53 appear to be generic and will be searched along with the first species.

Claims 5,48 and 49 appear to be subgeneric to groups II and III and will be searched along with either species.

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